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(12) **United States Patent**  
**Ibbetson et al.**

(10) **Patent No.:** **US 8,710,536 B2**  
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(54) **COMPOSITE HIGH REFLECTIVITY LAYER**

(71) Applicant: **Cree, Inc.**, Durham, NC (US)

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**Related U.S. Application Data**

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(51) **Int. Cl.**  
**H01L 33/00** (2010.01)

(52) **U.S. Cl.**  
USPC ..... **257/98**; 257/E33.055; 257/E33.057

(58) **Field of Classification Search**  
CPC ..... H01L 33/10; H01L 33/46; H01L 33/60  
USPC ..... 257/98, 13, E33.055, E33.057  
See application file for complete search history.

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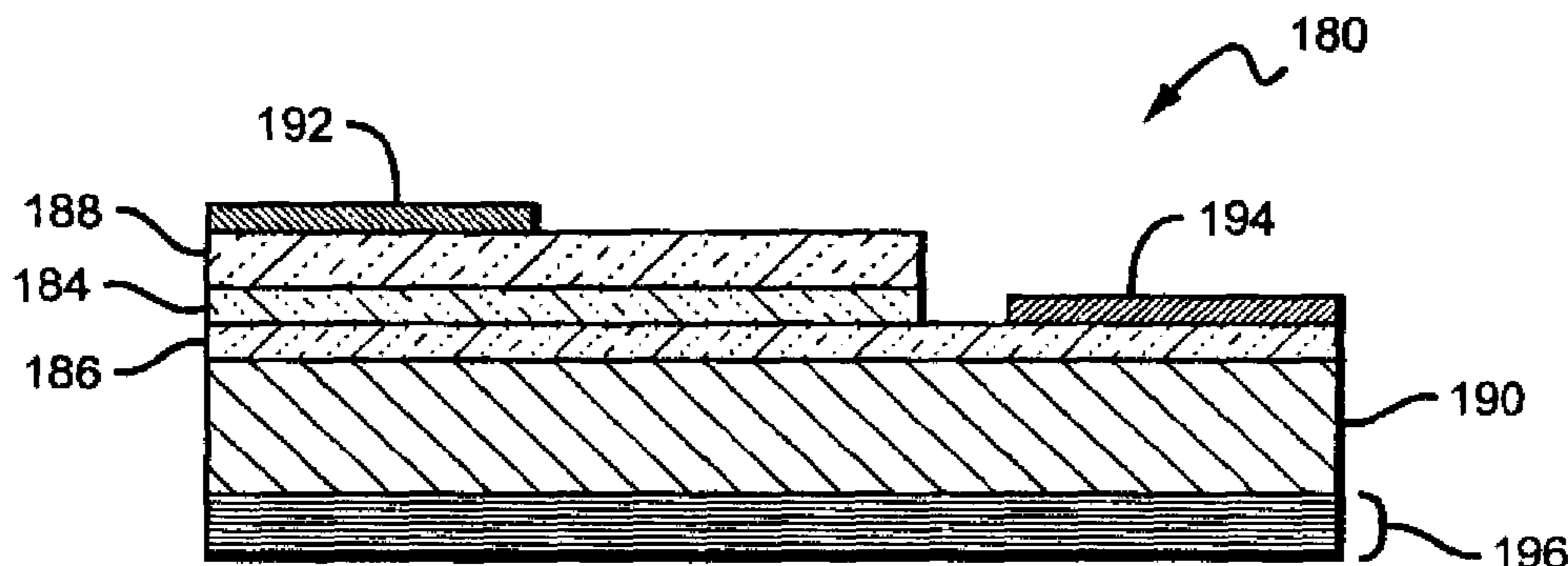
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(57) **ABSTRACT**

A high efficiency light emitting diode with a composite high reflectivity layer integral to said LED to improve emission efficiency. One embodiment of a light emitting diode (LED) chip comprises an LED and a composite high reflectivity layer integral to the LED to reflect light emitted from the active region. The composite layer comprises a first layer, and alternating plurality of second and third layers on the first layer, and a reflective layer on the topmost of said plurality of second and third layers. The second and third layers have a different index of refraction, and the first layer is at least three times thicker than the thickest of the second and third layers. For composite layers internal to the LED chip, conductive vias can be included through the composite layer to allow an electrical signal to pass through the composite layer to the LED.

**15 Claims, 6 Drawing Sheets**



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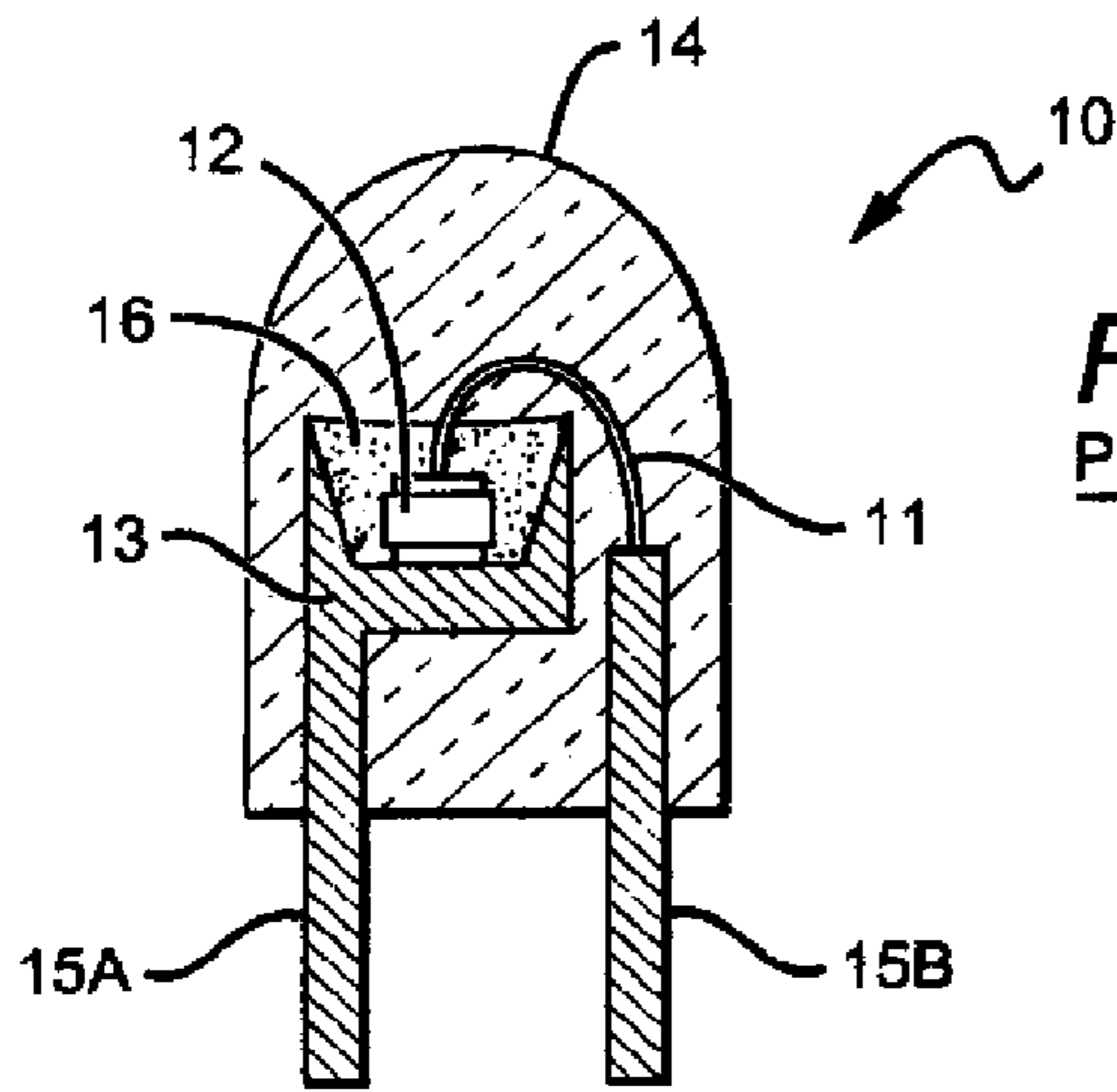
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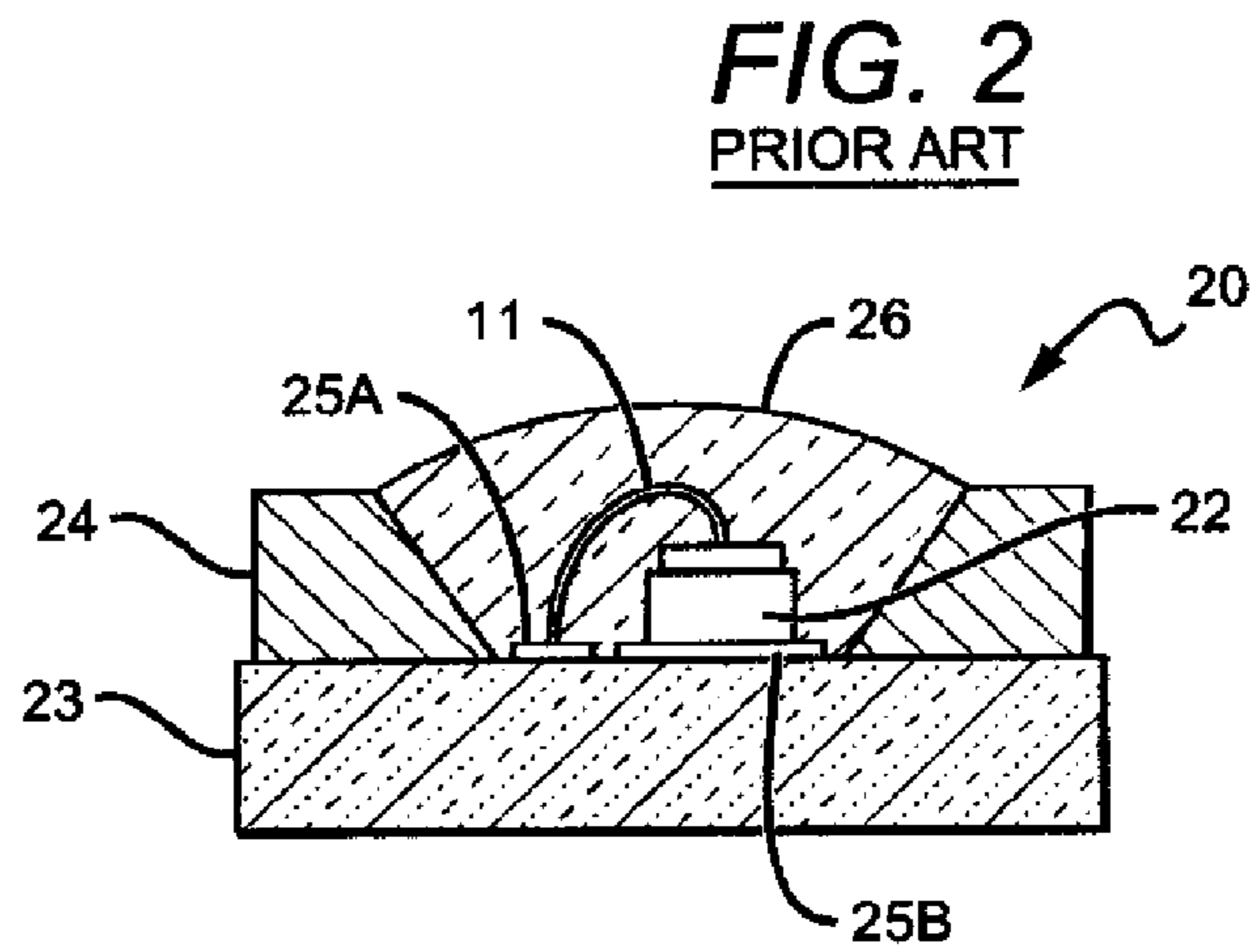
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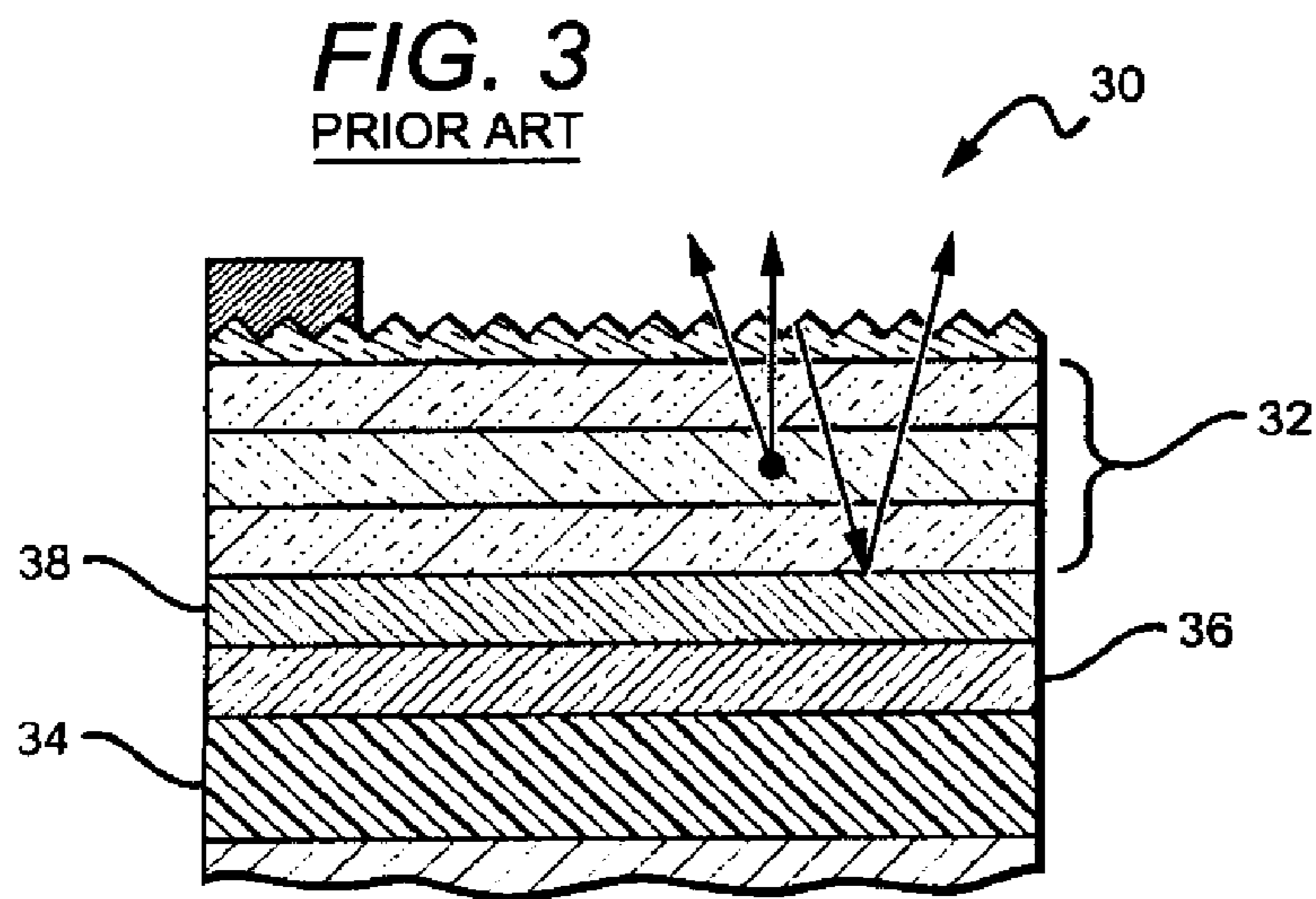
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**FIG. 1**  
**PRIOR ART**



**FIG. 2**  
**PRIOR ART**



**FIG. 3**  
**PRIOR ART**

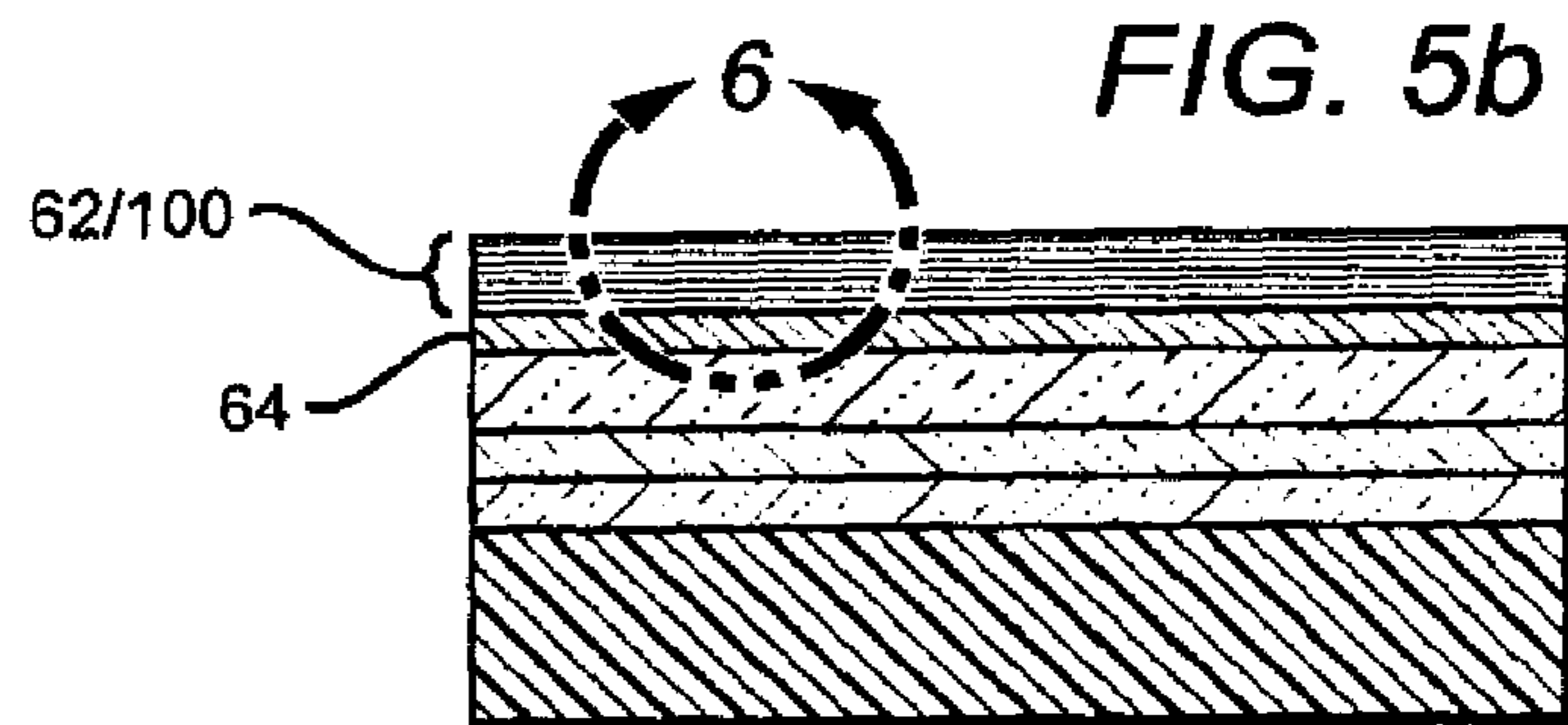
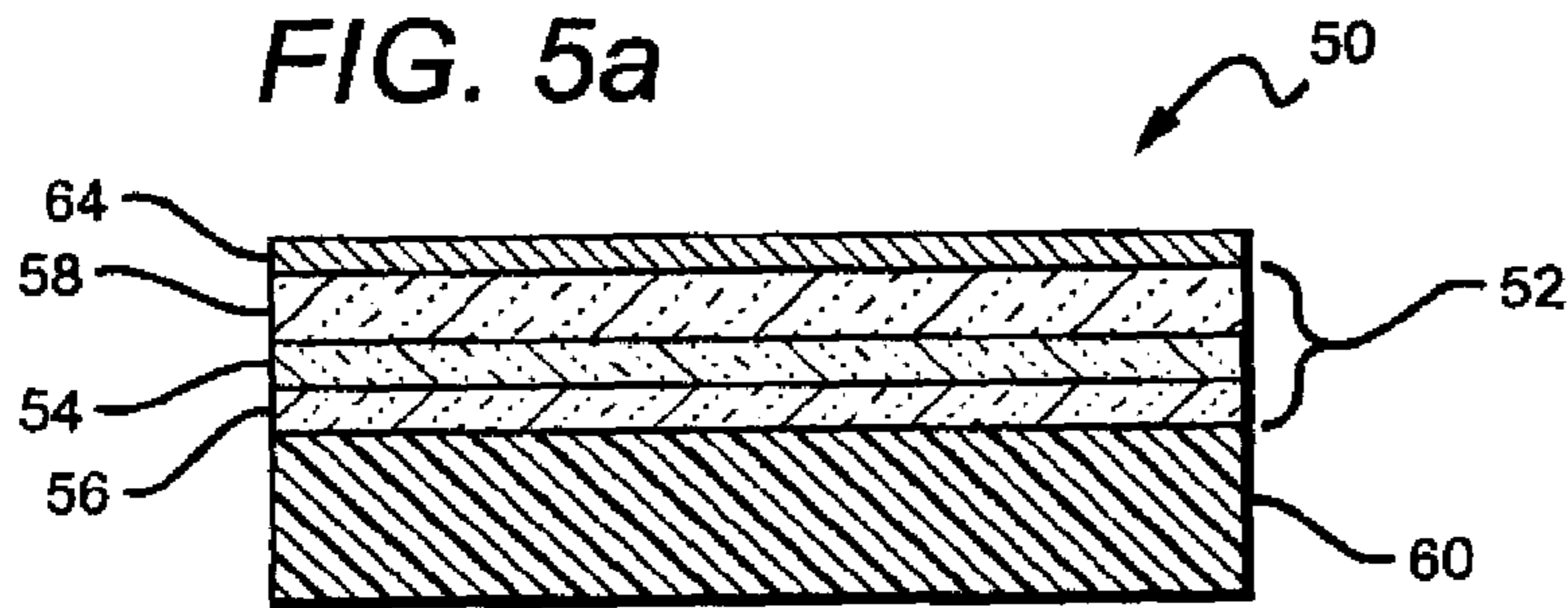
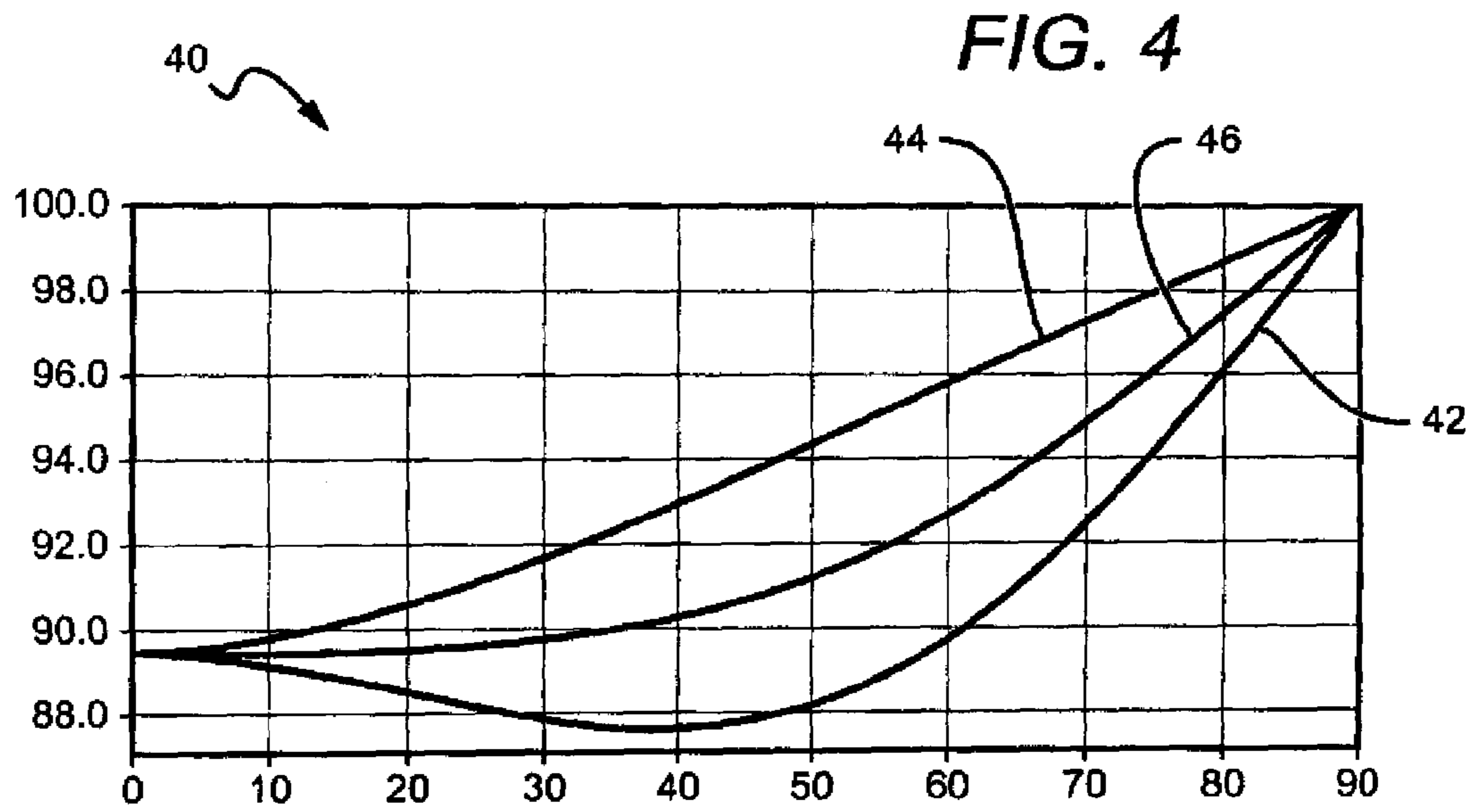


FIG. 6

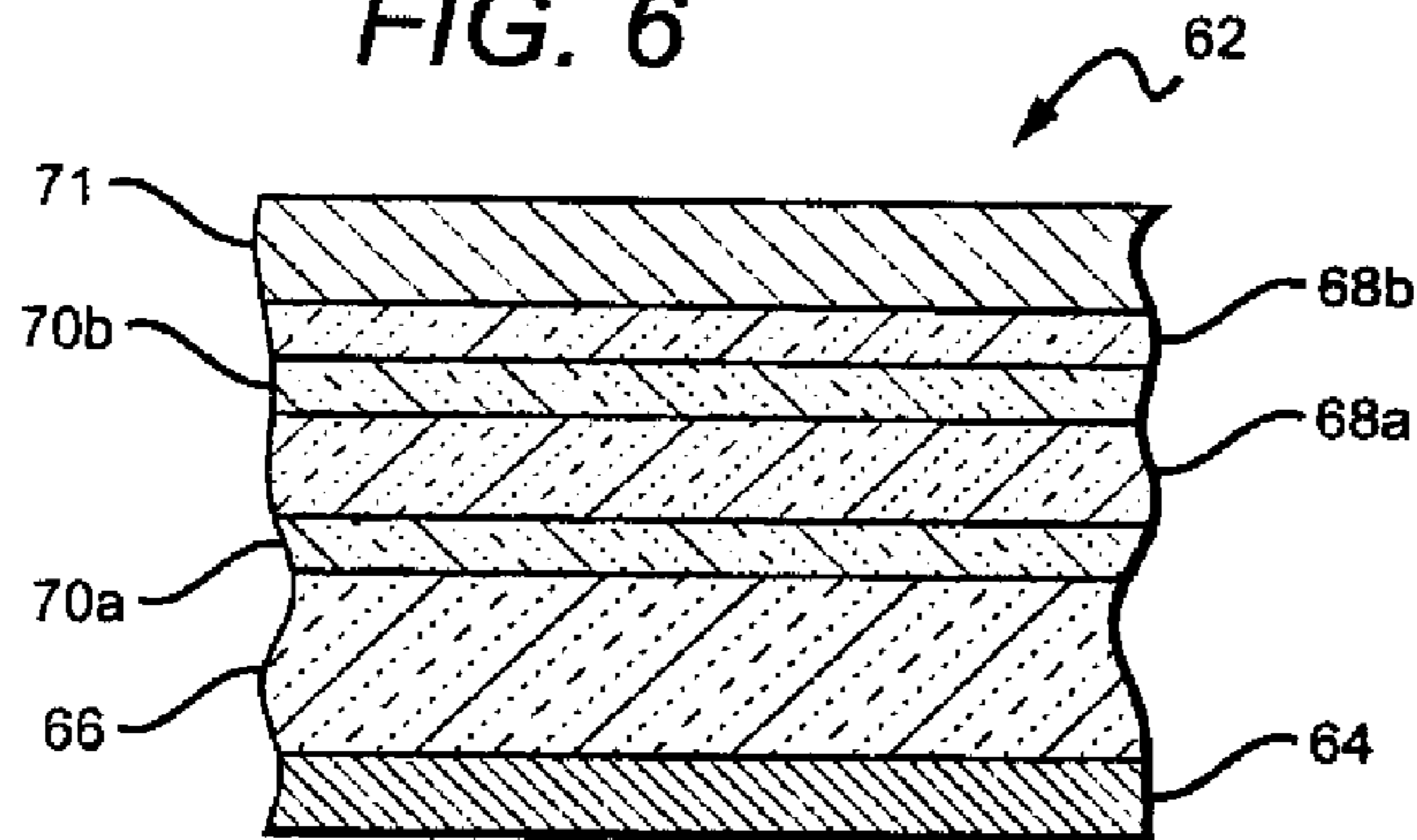


FIG. 9

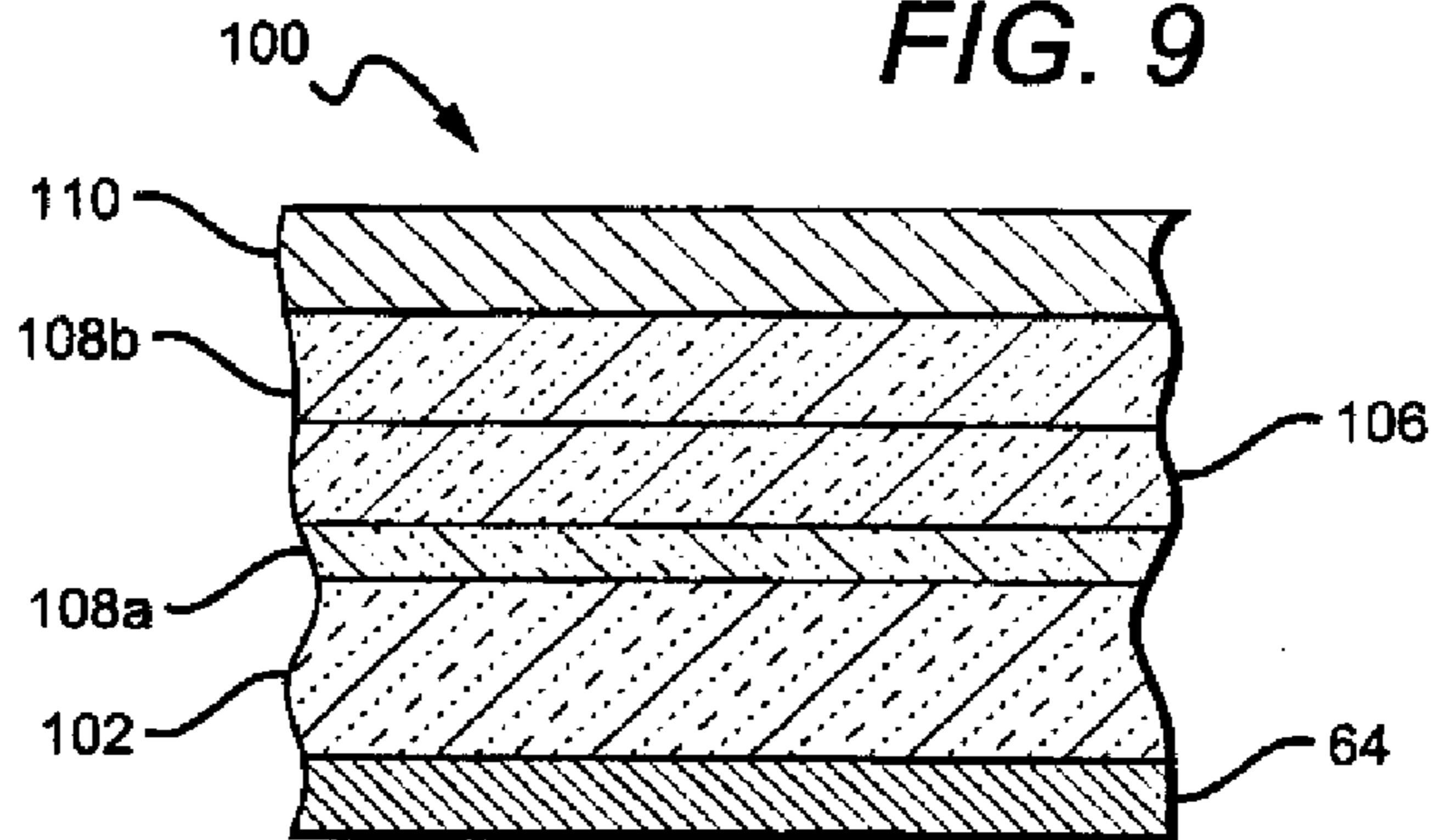


FIG. 7

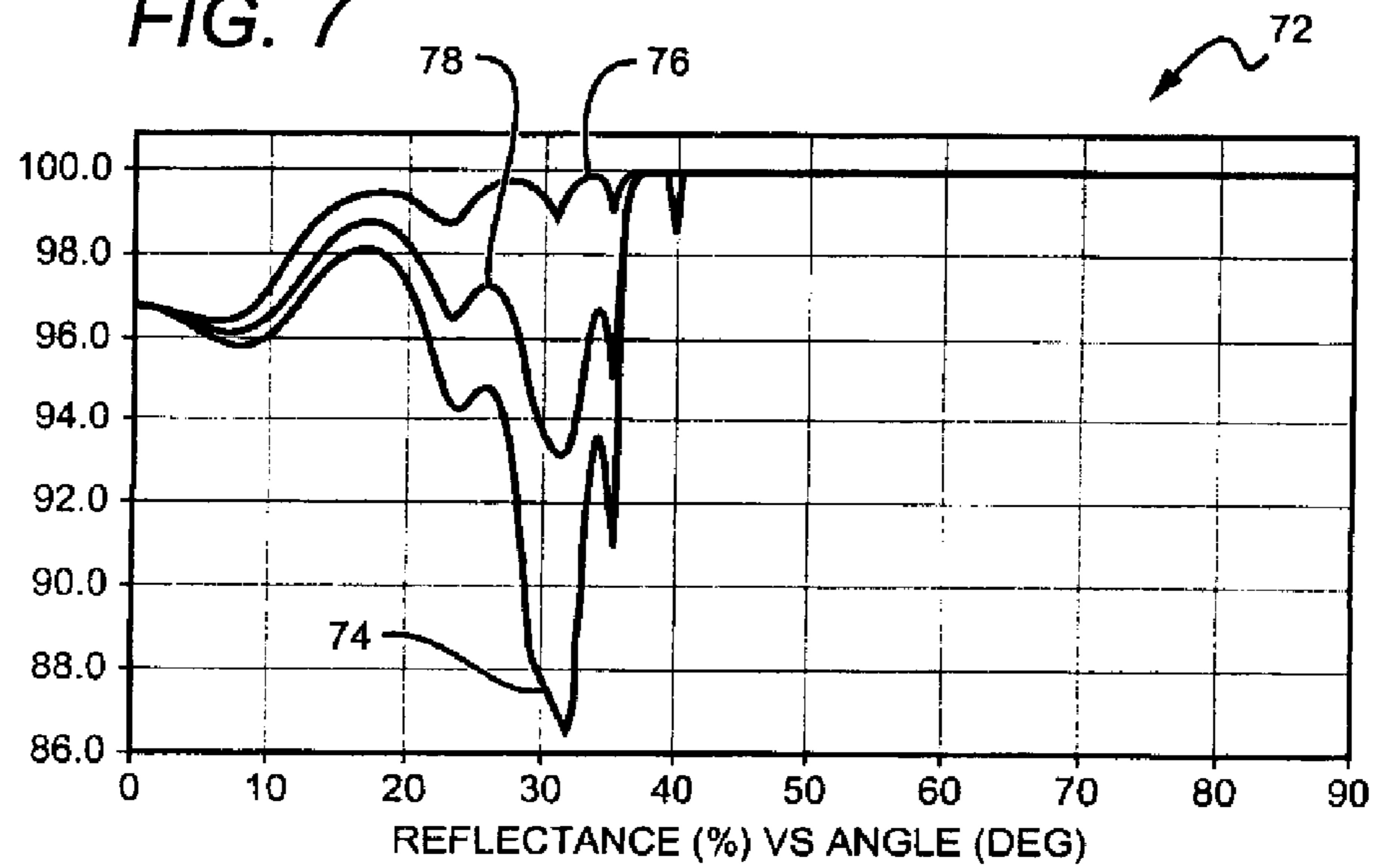


FIG. 8

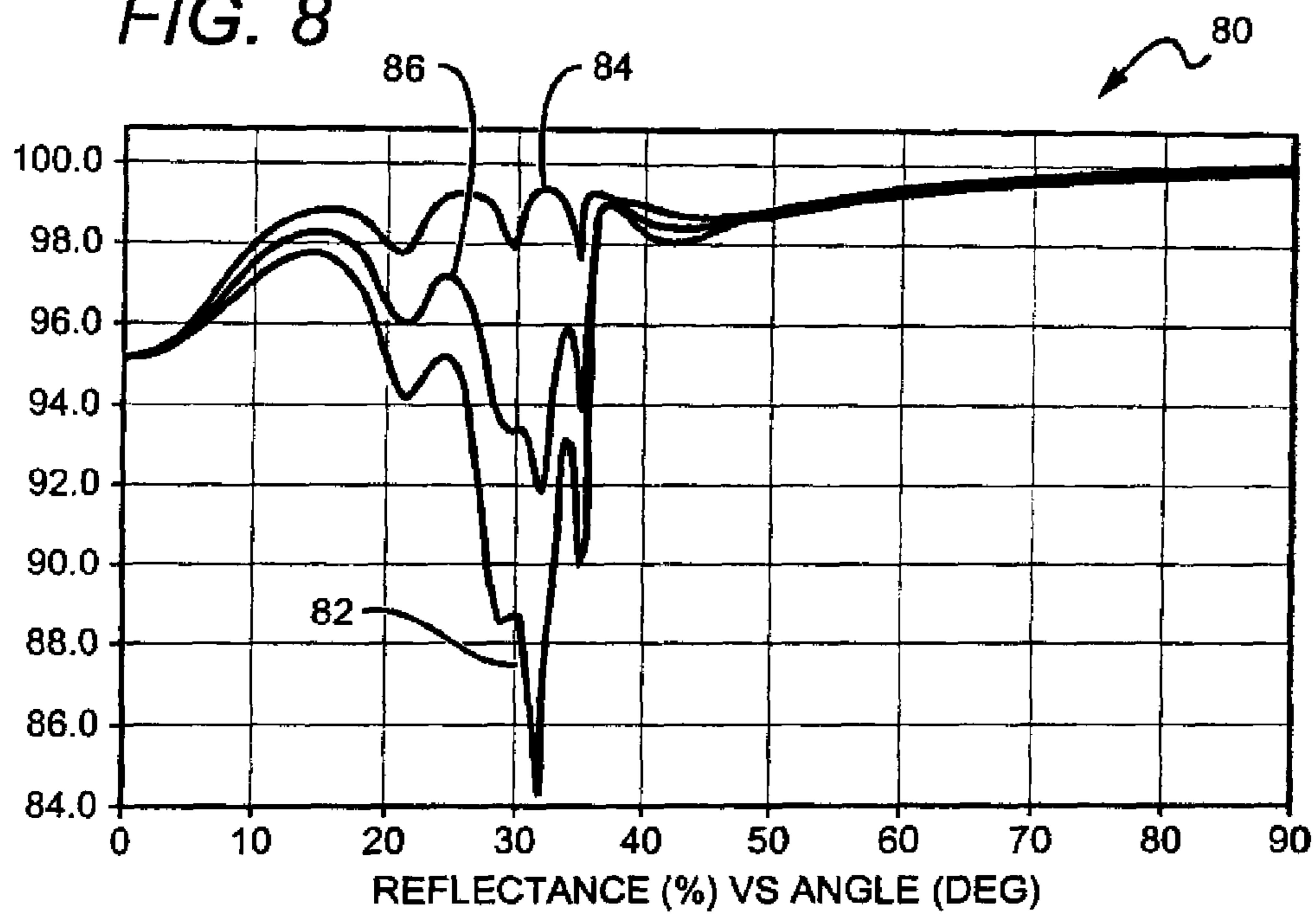


FIG. 10a

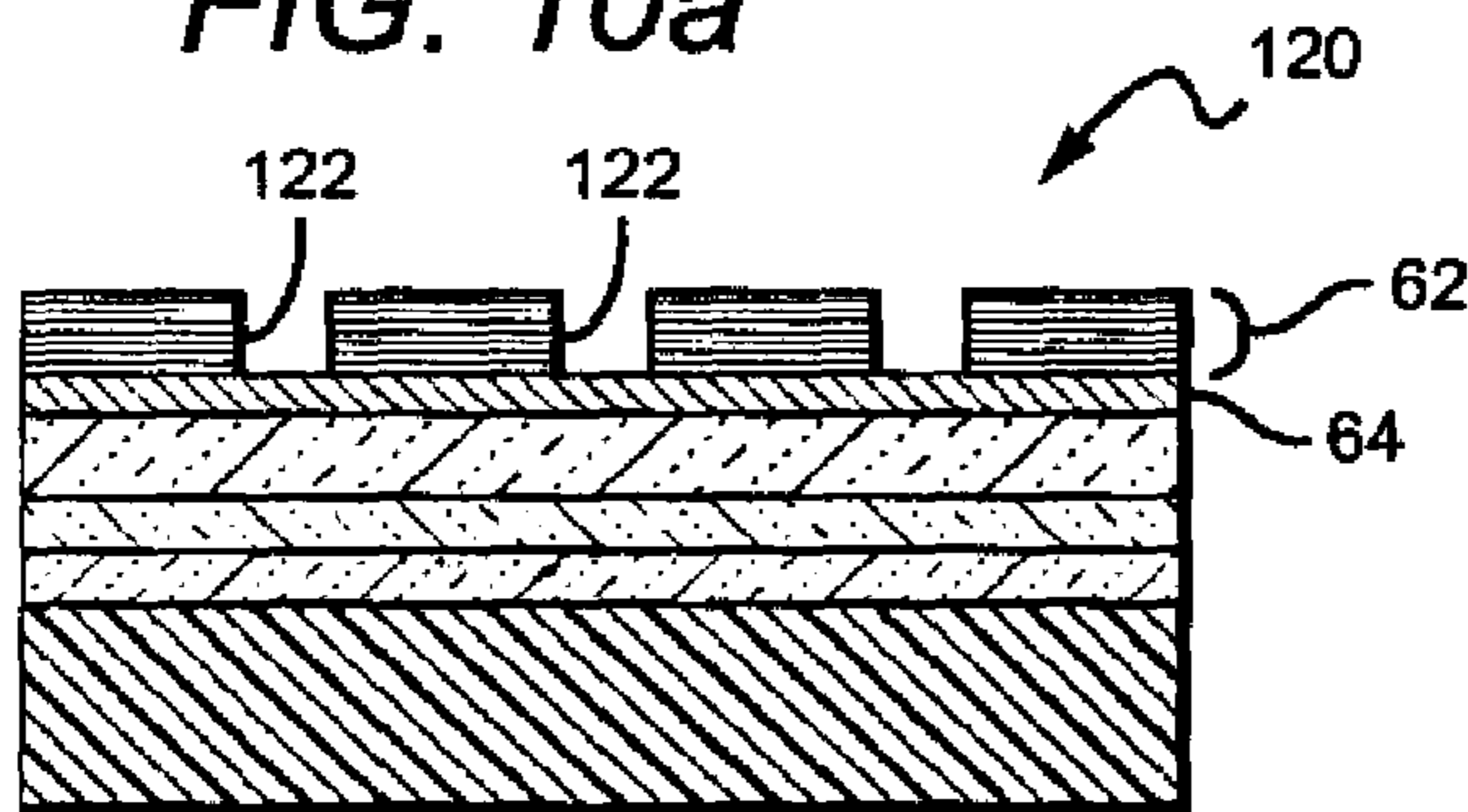
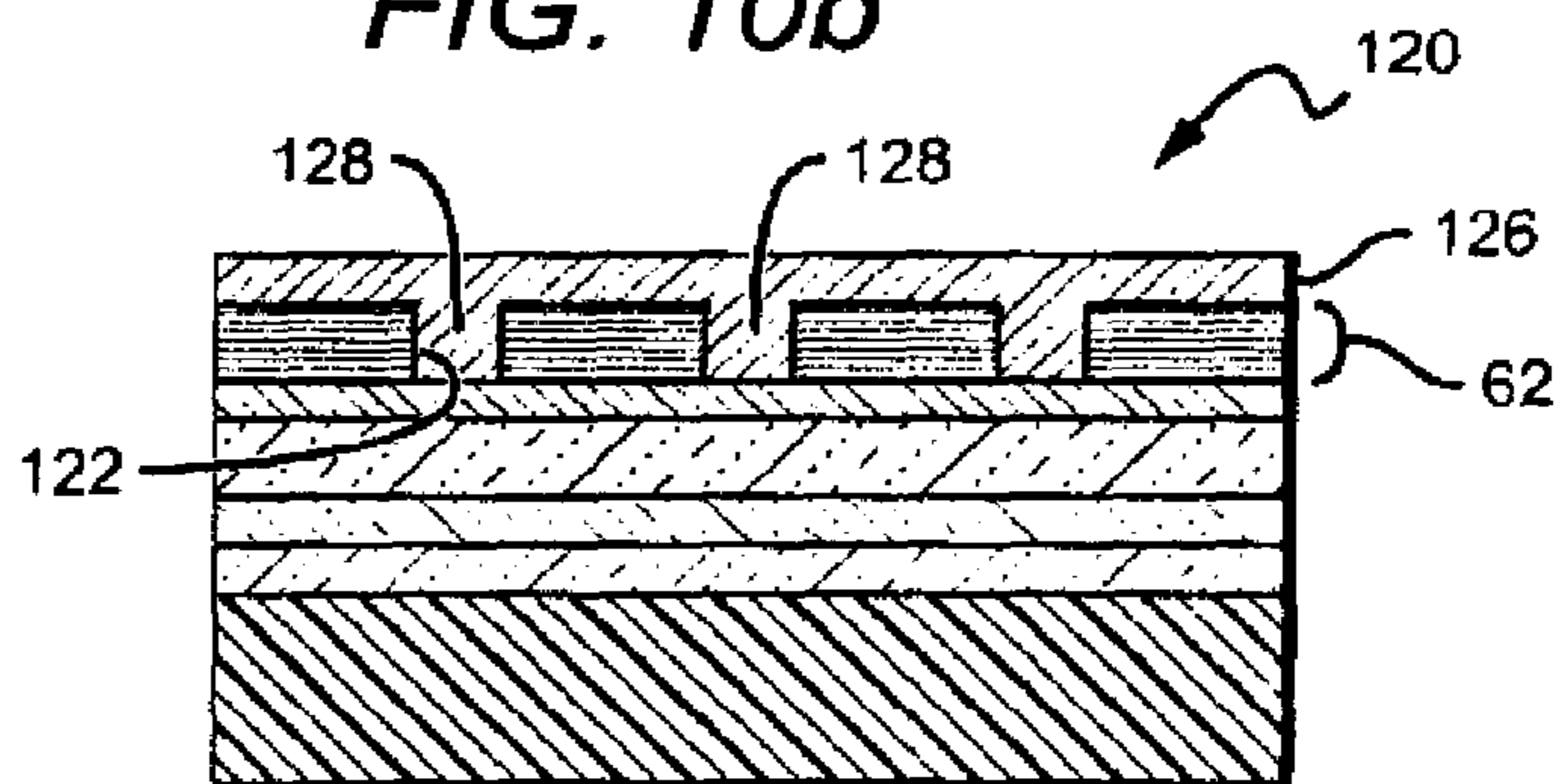


FIG. 10b



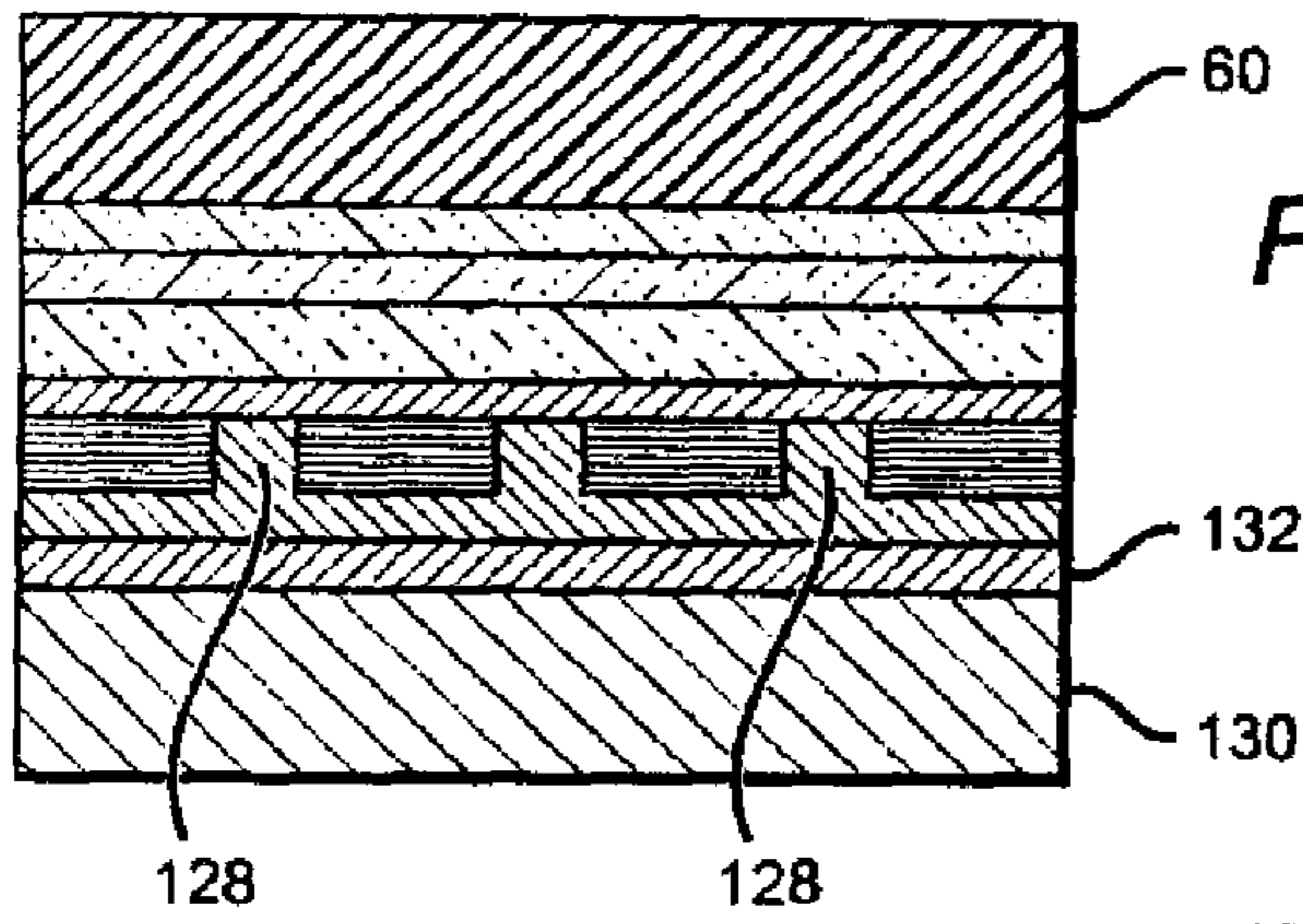


FIG. 10c

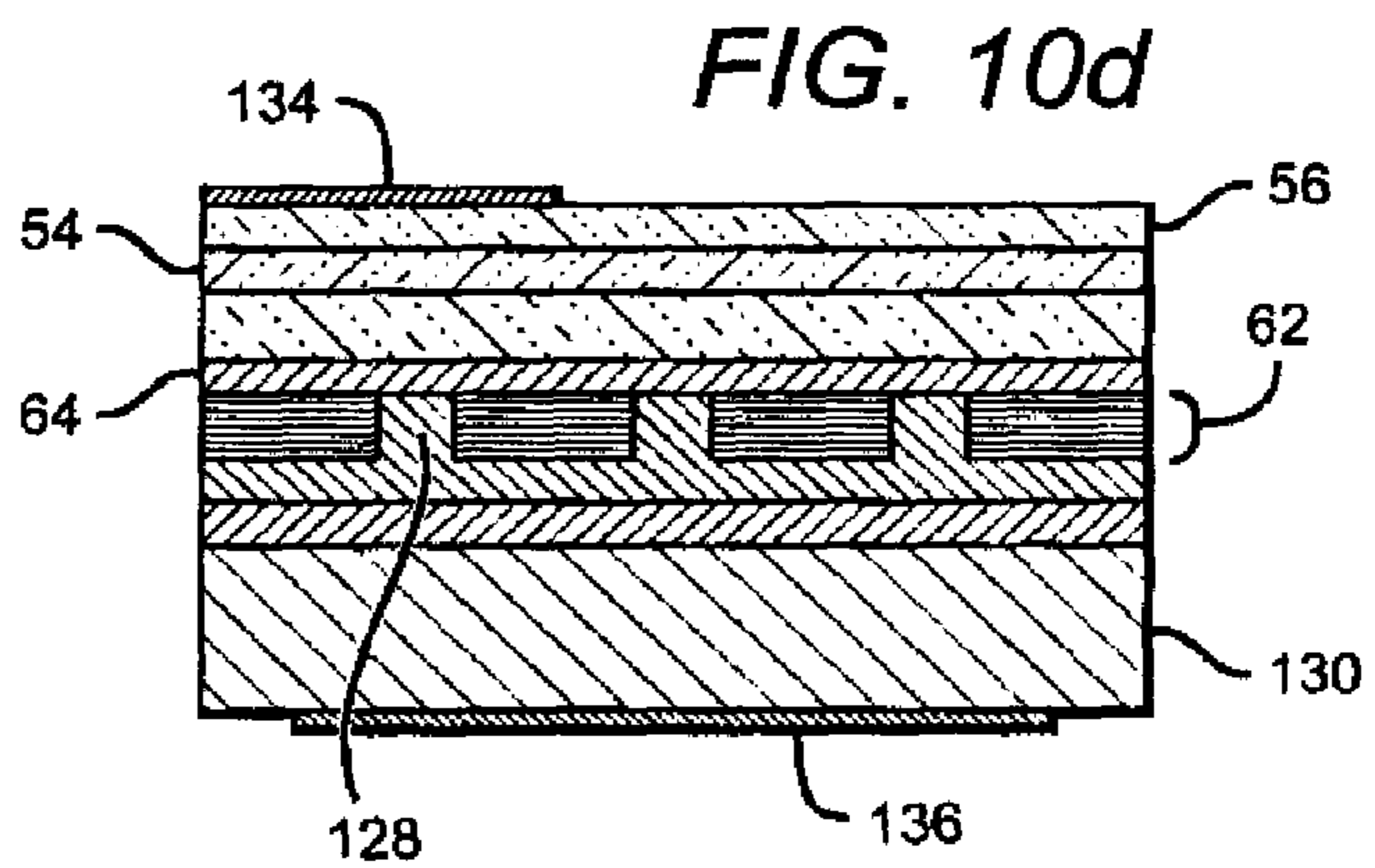


FIG. 10d

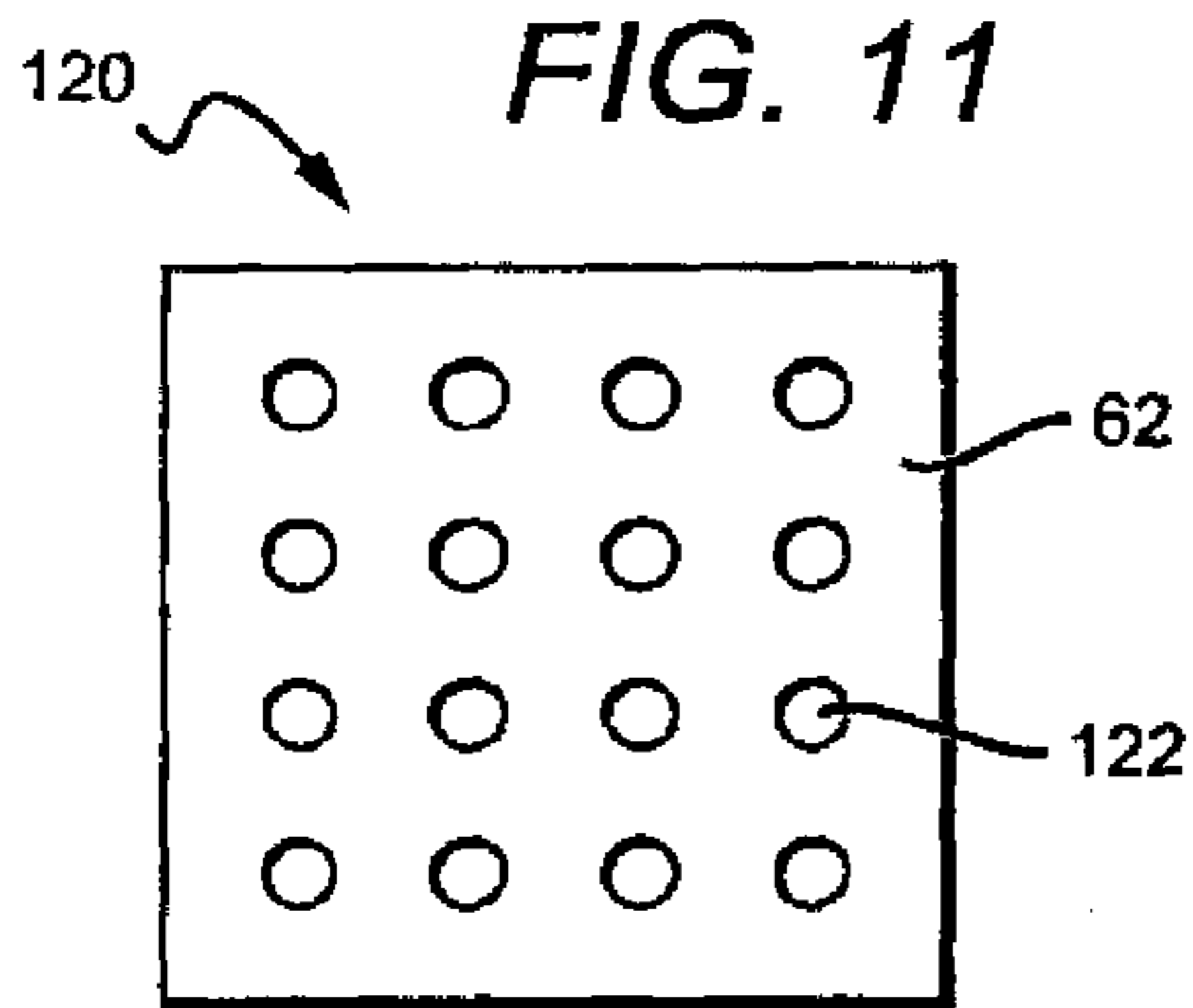


FIG. 11

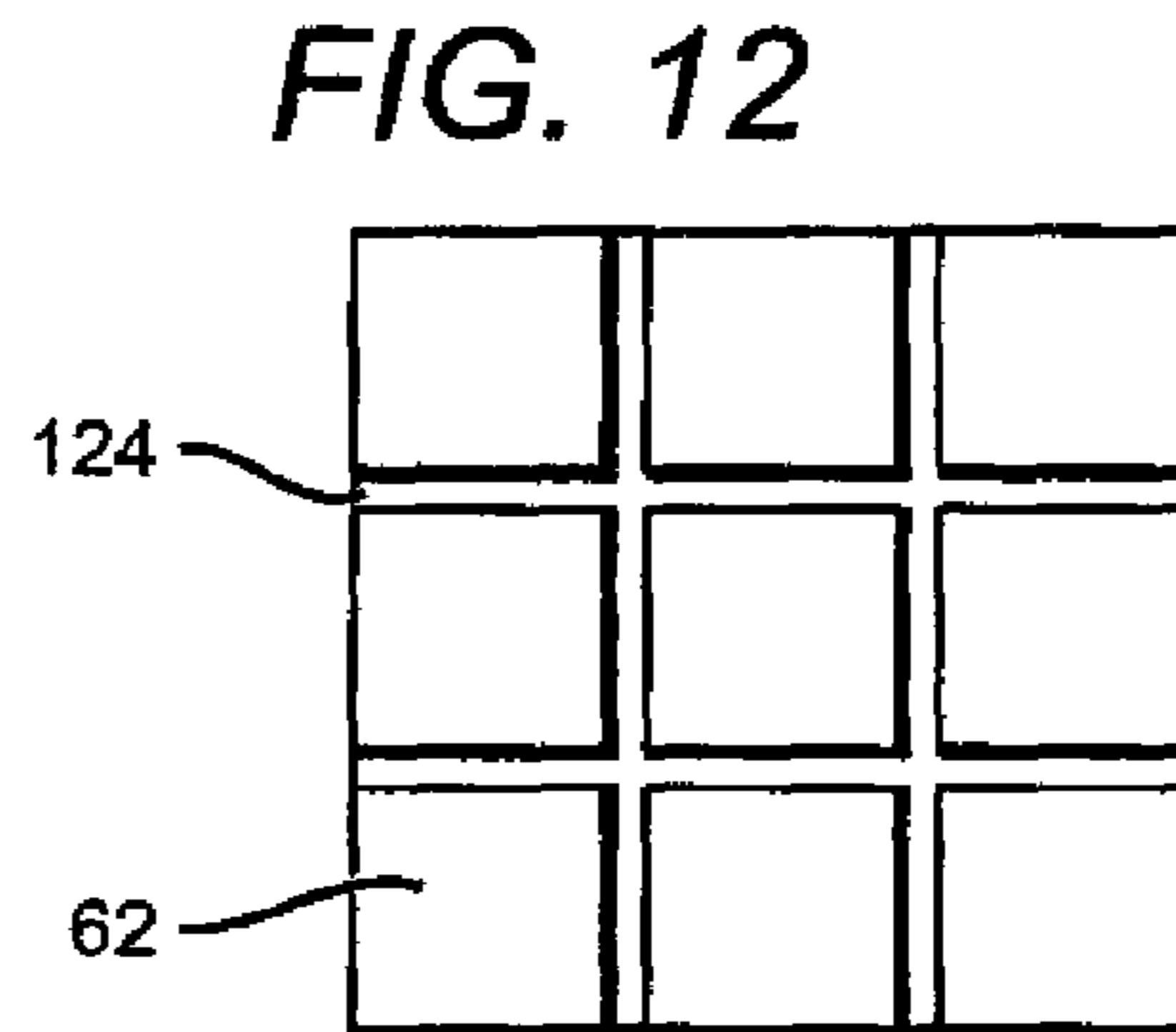


FIG. 12

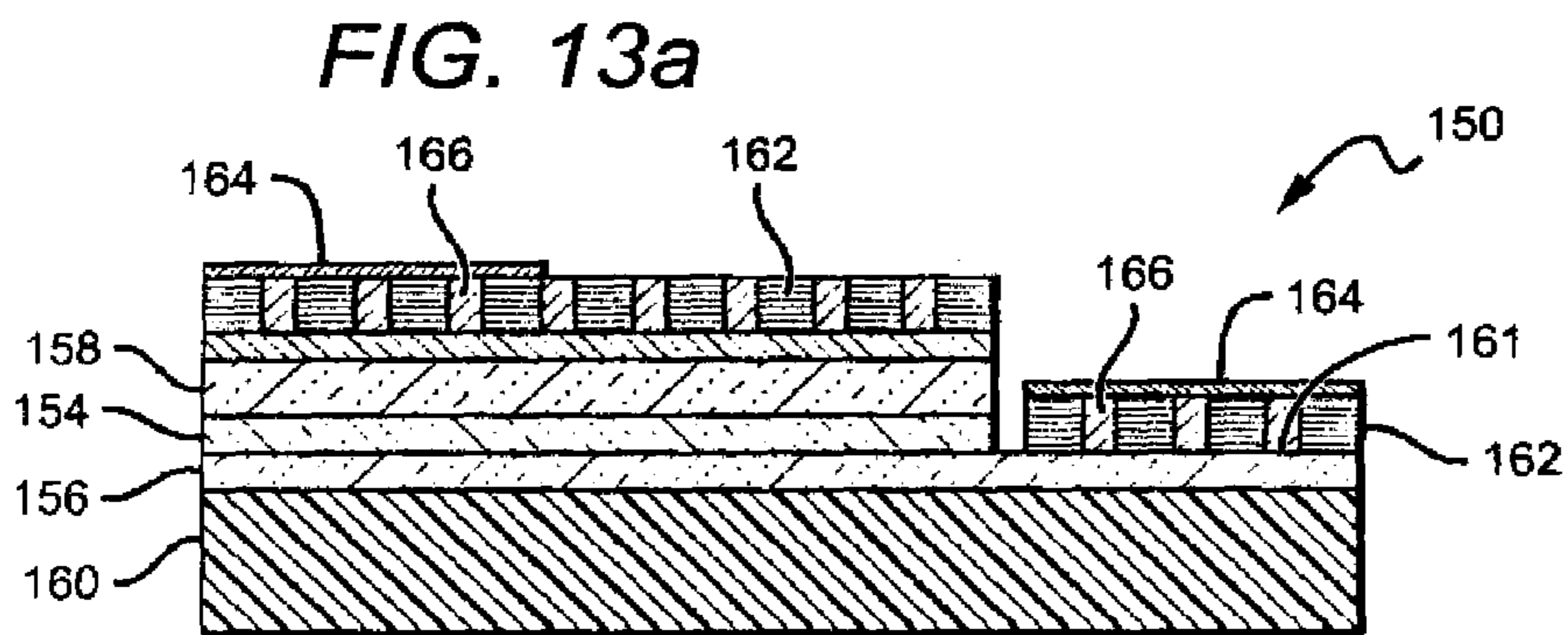
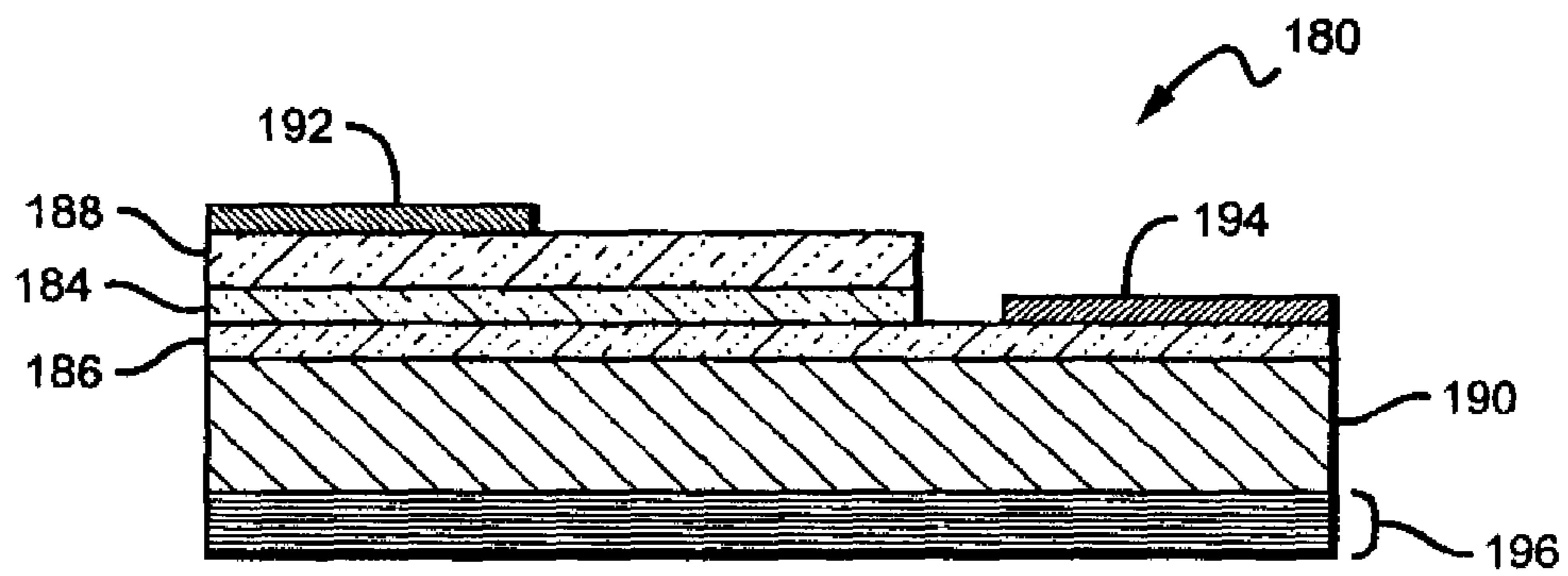
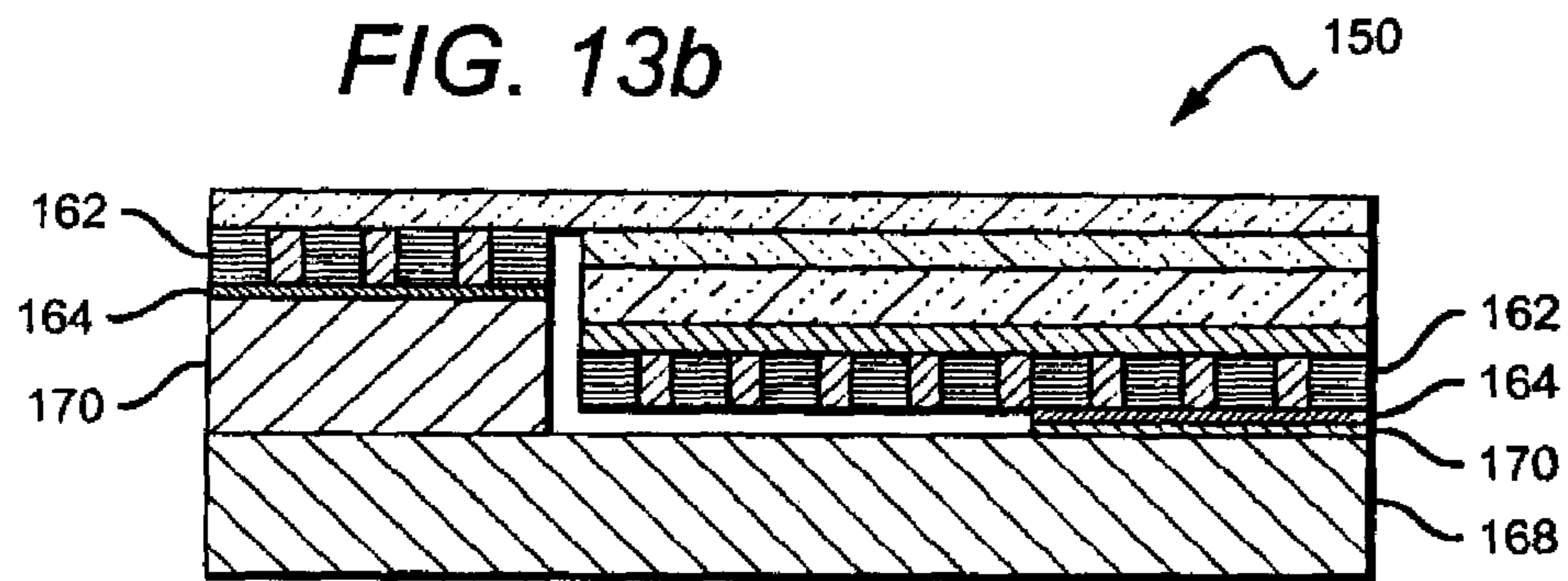
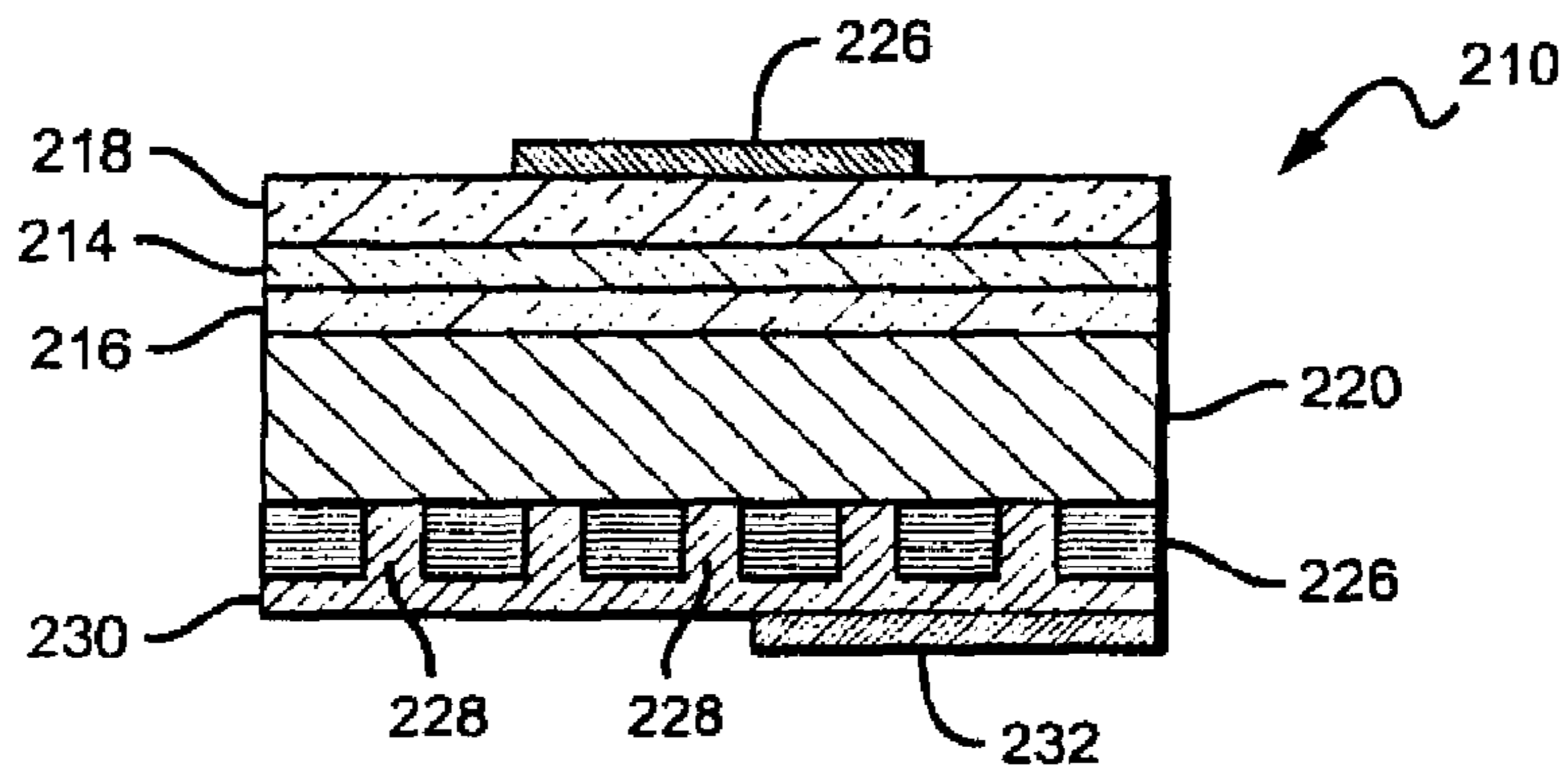


FIG. 13a





**FIG. 14**



**FIG. 15**

**COMPOSITE HIGH REFLECTIVITY LAYER**

This application is a divisional of U.S. patent application Ser. No. 13/071,349, to Ibbetson et al., filed on Mar. 24, 2011, which is a continuation of and claims the benefit of, U.S. patent application Ser. No. 12/316,097 to Ibbetson et al., filed on Dec. 8, 2008.

**BACKGROUND OF THE INVENTION****1. Field of the Invention**

This invention relates to light emitting diodes, and to light emitting diodes with a high reflectivity contact and method for forming the contact.

**2. Description of the Related Art**

Light emitting diodes (LED or LEDs) are solid state devices that convert electric energy to light, and generally comprise one or more active layers of semiconductor material sandwiched between oppositely doped n-type and p-type layers. When a bias is applied across the doped layers, holes and electrons are injected into the active layer where they recombine to generate light. Light is emitted from the active layer and from all surfaces of the LED.

For typical LEDs it is desirable to operate at the highest light emission efficiency, and one way that emission efficiency can be measured is by the emission intensity in relation to the input power, or lumens per watt. One way to maximize emission efficiency is by maximizing extraction of light emitted by the active region of LEDs. For conventional LEDs with a single out-coupling surface, the external quantum efficiency can be limited by total internal reflection (TIR) of light from the LED's emission region. TIR can be caused by the large difference in the refractive index between the LED's semiconductor and surrounding ambient. Some LEDs have relatively low light extraction efficiencies because the high index of refraction of the substrate compared to the index of refraction for the surrounding material, such as epoxy. This difference results in a small escape cone from which light rays from the active area can transmit from the substrate into the epoxy and ultimately escape from the LED package. Light that does not escape can be absorbed in the semiconductor material or at surfaces that reflect the light.

Different approaches have been developed to reduce TIR and improve overall light extraction, with one of the more popular being surface texturing. Surface texturing increases the light escape probability by providing a varying surface that allows photons multiple opportunities to find an escape cone. Light that does not find an escape cone continues to experience TIR, and reflects off the textured surface at different angles until it finds an escape cone. The benefits of surface texturing have been discussed in several articles. [See Windisch et al., *Impact of Texture-Enhanced Transmission on High-Efficiency Surface Textured Light Emitting Diodes*, Appl. Phys. Lett., Vol. 79, No. 15, October 2001, Pgs. 2316-2317; Schnitzer et al. *30% External Quantum Efficiency From Surface Textured, Thin Film Light Emitting Diodes*, Appl. Phys. Lett., Vol 64, No. 16, Oct. 1993, Pgs. 2174-2176; Windisch et al. *Light Extraction Mechanisms in High-Efficiency Surface Textured Light Emitting Diodes*, IEEE Journal on Selected Topics in Quantum Electronics, Vol. 8, No. 2, Mar./April 2002, Pgs. 248-255; Streubel et al. *High Brightness AlGaInP Light Emitting Diodes*, IEEE Journal on Selected Topics in Quantum Electronics, Vol. 8, No. March/April 2002].

U.S. Pat. No. 6,657,236, also assigned to Cree Inc., discloses structures formed on the semiconductor layers for enhancing light extraction in LEDs.

Another way to increase light extraction efficiency is to provide reflective surfaces that reflect light so that it contributes to useful emission from the LED chip or LED package. In a typical LED package **10** illustrated in FIG. **1**, a single LED chip **12** is mounted on a reflective cup **13** by means of a solder bond or conductive epoxy. One or more wire bonds **11** connect the ohmic contacts of the LED chip **12** to leads **15A** and/or **15B**, which may be attached to or integral with the reflective cup **13**. The reflective cup may be filled with an encapsulant material **16** which may contain a wavelength conversion material such as a phosphor. Light emitted by the LED at a first wavelength may be absorbed by the phosphor, which may responsively emit light at a second wavelength. The entire assembly is then encapsulated in a clear protective resin **14**, which may be molded in the shape of a lens to collimate the light emitted from the LED chip **12**. While the reflective cup **13** may direct light in an upward direction, optical losses may occur when the light is reflected. Some light may be absorbed by the reflector cup due to the less than 100% reflectivity of practical reflector surfaces. Some metals can have less than 95% reflectivity in the wavelength range of interest.

FIG. **2** shows another LED package in which one or more LED chips **22** can be mounted onto a carrier such as a printed circuit board (PCB) carrier, substrate or submount **23**. A metal reflector **24** mounted on the submount surrounds the LED chip(s) **22** and reflects light emitted by the LED chips **22** away from the package **20**. The reflector **24** also provides mechanical protection to the LED chips **22**. One or more wirebond connections **11** are made between ohmic contacts on the LED chips **22** and electrical traces **25A**, **25B** on the submount **23**. The mounted LED chips **22** are then covered with an encapsulant **26**, which may provide environmental and mechanical protection to the chips while also acting as a lens. The metal reflector **24** is typically attached to the carrier by means of a solder or epoxy bond. The metal reflector **24** may also experience optical losses when the light is reflected because it also has less than 100% reflectivity.

The reflectors shown in FIGS. **1** and **2** are arranged to reflect light that escapes from the LED. LEDs have also been developed having internal reflective surfaces to reflect light internal to the LEDs. FIG. **3** shows a schematic of an LED chip **30** with an LED **32** mounted on a submount **34** by a metal bond layer **36**. The LED further comprises a p-contact/reflector **38** between the LED **32** and the metal bond **36**, with the reflector **38** typically comprising a metal such as silver (Ag). This arrangement is utilized in commercially available LEDs such as those from Cree® Inc., available under the EZBright™ family of LEDs. The reflector **38** can reflect light emitted from the LED chip toward the submount back toward the LED's primary emitting surface. The reflector also reflects TIR light back toward the LED's primary emitting surface. Like the metal reflectors above, reflector **38** reflects less than 100% of light and in some cases less than 95%. The reflectivity of a metal film on a semiconductor layer may be calculated from the materials' optical constants using thin film design software such as TFCalc™ from Software Spectra, Inc. ([www.sspectra.com](http://www.sspectra.com)).

FIG. **4** shows a graph **40** showing the reflectivity of Ag on gallium nitride (GaN) at different viewing angles for light with a wavelength of 460 nm. The refractive index of GaN is 2.47, while the complex refractive index for silver is taken from the technical literature. [See *Handbook of Optical Constants of Solids*, edited by E. Palik.] The graph shows the p-polarization reflectivity **42**, s-polarization reflectivity **44**, and average reflectivity **46**, with the average reflectivity **46** generally illustrating the overall reflectivity of the metal for

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the purpose of LEDs where light is generated with random polarization. The reflectivity at 0 degrees is lower than the reflectivity at 90 degrees, and this difference can result in up to 5% or more of the light being lost on each reflection. In a LED chip, in some instances TIR light can reflect off the mirror several times before it escapes and, as a result, small changes in the mirror absorption can lead to significant changes in the brightness of the LED. The cumulative effect of the mirror absorption on each reflection can reduce the light intensity such that less than 75% of light from the LED's active region actually escapes as LED light.

#### SUMMARY OF THE INVENTION

The present invention discloses a higher reflectivity layer for use in LEDs and LED chips to increase emission efficiency. One embodiment of a light emitting diode (LED) chip according to the present invention comprises an active region between two oppositely doped layers. A composite high reflectivity layer is arranged to reflect light emitted from the active region. The composite layer comprises a first layer, one or more second layers, and a plurality of third layers on the first layer. The second layers have an index of refraction different from the third layers. The second and third layers alternate, and each of the third layers having different thicknesses compared to the other of the third layers. A reflective layer is included on the topmost of the second and third layers

Another embodiment of an LED chip according to the present invention comprises a submount with an LED mounted to the submount. A composite high reflectivity layer is arranged between the submount and the LED to reflect LED light. The composite layer comprises a plurality of layers and a conductive path through the composite layer through which an electrical signal can pass to the LED.

Another embodiment of an LED chip according to the present invention comprises an LED and a composite high reflectivity layer integral to the LED to reflect light emitted from the active region. The composite layer comprises a first layer, and alternating plurality of second and third layers on the first layer. The second and third layers have a different index of refraction, and the first layer is at least three times thicker than the thickest of the second and third layers.

In still another embodiment of an LED chip according to the present invention comprises an LED and a composite high reflectivity layer integral to the LED to reflect light emitted from the LED. The composite layer comprising a first layer, and one or more second layers and a plurality of third layers on the first layer, with the second and third layers comprising incomplete second and third layer pairs.

These and other aspects and advantages of the invention will become apparent from the following detailed description and the accompanying drawings, which illustrate by way of example the features of the invention.

#### BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a sectional view of one embodiment of a prior art LED lamp;

FIG. 2 is a sectional view of another embodiment of a prior art LED lamp;

FIG. 3 is a sectional view of another embodiment of a prior art LED chip;

FIG. 4 is a graph showing the reflectivity of a metal reflector at different viewing angles;

FIG. 5a is a sectional view of one embodiment of an LED chip at a fabrication step in one method according to the present invention;

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FIG. 5b is a sectional view of the LED chip in FIG. 5a at a subsequent fabrication step;

FIG. 6 is a sectional view of one embodiment of composite layer according to the present invention;

FIG. 7 is a graph showing the reflectivity of a composite layer according to the present invention;

FIG. 8 is a graph showing the reflectivity of a composite layer according to the present invention;

FIG. 9 is a sectional view of another embodiment of a composite layer according to the present invention;

FIG. 10a is a sectional view of another embodiment of an LED according to the present invention;

FIG. 10b is a sectional view of the LED in FIG. 10a at a subsequent fabrication step;

FIG. 10c is a sectional view of the LED in FIG. 10b at a subsequent fabrication step;

FIG. 10d is a sectional view of the LED in FIG. 10c at a subsequent fabrication step;

FIG. 11 is a plan view of one embodiment of a composite layer according to the present invention;

FIG. 12 is a plan view of another embodiment of a composite layer according to the present invention;

FIG. 13a is a sectional view of another embodiment of an LED chip according to the present invention;

FIG. 13b is a sectional view of the LED chip shown in FIG. 13a at a subsequent fabrication step;

FIG. 14 is a sectional view of another embodiment of an LED chip according to the present invention; and

FIG. 15 is a sectional view of still another embodiment of an LED chip according to the present invention.

#### DETAILED DESCRIPTION OF THE INVENTION

The present invention is directed to solid-state emitters and methods for fabricating solid-state emitters having one or more composite high reflectivity contacts or layers arranged to increase emission efficiency of the emitters. The present invention is described herein with reference to light emitting diodes (LED or LEDs) but it is understood that it is equally applicable to other solid-state emitters. The present invention can be used as a reflector in conjunction with one or more contacts, or can be used as a reflector separate from the contacts.

The improved reflectivity of the composite contact/layer ("composite layer") reduces optical losses that can occur in reflecting light that is emitted from the active region in a direction away from useful light emission, such as toward the substrate or submount, and also to reduce losses that can occur when TIR light is reflecting within the LED. Embodiments of the present invention provide various unique combinations of layers that can comprise a composite layer. In one embodiment according to the present invention, the composite layer can comprise a first relatively thick layer, with second and third layers having different indices of refraction and different thickness, and a reflective layer. The composite layer can be in many different locations such as on an outer surface of the LED or internal to the LED.

Different embodiments of the invention also provide composite layers having conductive via or path arrangements that provide conductive paths through the composite layer. This allows an electric signal to pass through the composite layer along the vias so that the composite layer can be used as an internal layer, where an electrical signal passes through the composite layer during operation. This via arrangement can take many different shapes and sizes as described in detail below.

The present invention is described herein with reference to certain embodiments but it is understood that the invention can be embodied in many different forms and should not be construed as limited to the embodiments set forth herein. In particular, the composite layer can comprise many different layers of different material with many different thicknesses beyond those described herein. The composite layer can be in many different locations on different solid-state emitters beyond those described herein. Further, the composite layer can be provided with or without conductive structures to allow electrical signals to pass through.

It is also understood that when an element such as a layer, region or substrate is referred to as being “on” another element, it can be directly on the other element or intervening elements may also be present. Furthermore, relative terms such as “inner”, “outer”, “upper”, “above”, “lower”, “beneath”, and “below”, and similar terms, may be used herein to describe a relationship of one layer or another region. It is understood that these terms are intended to encompass different orientations of the device in addition to the orientation depicted in the figures.

Although the terms first, second, etc. may be used herein to describe various elements, components, regions, layers and/or sections, these elements, components, regions, layers and/or sections should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer or section from another region, layer or section. Thus, a first element, component, region, layer or section discussed below could be termed a second element, component, region, layer or section without departing from the teachings of the present invention.

Embodiments of the invention are described herein with reference to cross-sectional view illustrations that are schematic illustrations of embodiments of the invention. As such, the actual thickness of the layers can be different, and variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances are expected. Embodiments of the invention should not be construed as limited to the particular shapes of the regions illustrated herein but are to include deviations in shapes that result, for example, from manufacturing. A region illustrated or described as square or rectangular will typically have rounded or curved features due to normal manufacturing tolerances. Thus, the regions illustrated in the figures are schematic in nature and their shapes are not intended to illustrate the precise shape of a region of a device and are not intended to limit the scope of the invention.

FIGS. 5a and 5b show one embodiment of an LED chip 50 according to the present invention, and although the present invention is described with reference to fabrication of a single LED chip it is understood that the present invention can also be applied to wafer level LED fabrication, fabrication of groups of LEDs, or fabrication of packaged LED chips. The wafer or groups of LEDs can then be separated into individual LED chips using known singulation or dicing methods. This embodiment is also described with reference to an LED chip having vertical geometry arrangement and that is flip chip mounted. As further described below the present invention can be used with other LED arrangements, such as lateral geometry LEDs and non flip-chip orientations.

The LED chip 50 comprises an LED 52 that can have many different semiconductor layers arranged in different ways. The fabrication and operation of LEDs is generally known in the art and only briefly discussed herein. The layers of the LED 52 can be fabricated using known processes with a suitable process being fabrication using MOCVD. The layers of the LED 52 generally comprise an active layer/region 54

sandwiched between n-type and p-type oppositely doped epitaxial layers 56, 58, all of which are formed successively on a growth substrate 60. It is understood that additional layers and elements can also be included in the LED 52, including but not limited to buffer, nucleation, contact and current spreading layers as well as light extraction layers and elements. The active region 54 can comprise single quantum well (SQW), multiple quantum well (MQW), double heterostructure or super lattice structures.

The active region 54 and layers 56, 58 can be fabricated from different material systems, with preferred material systems being Group-III nitride based material systems. Group-III nitrides refer to those semiconductor compounds formed between nitrogen and the elements in the Group III of the periodic table, usually aluminum (Al), gallium (Ga), and indium (In). The term also refers to ternary and quaternary compounds such as aluminum gallium nitride (AlGaN) and aluminum indium gallium nitride (AlInGaN). In one embodiment, the n- and p-type layers 56, 58 are gallium nitride (GaN) and the active region 54 comprises InGaN. In alternative embodiments the n- and p-type layers 56, 58 may be AlGaN, aluminum gallium arsenide (AlGaAs) or aluminum gallium indium arsenide phosphide (AlGaInAsP) and related compounds.

The growth substrate 60 can be made of many materials such as sapphire, silicon carbide, aluminum nitride (AlN), GaN, with a suitable substrate being a 4H polytype of silicon carbide, although other silicon carbide polytypes can also be used including 3C, 6H and 15R polytypes. Silicon carbide has certain advantages, such as a closer crystal lattice match to Group III-nitrides than sapphire and results in Group III-nitride films of higher quality. Silicon carbide also has a very high thermal conductivity so that the total output power of Group-III nitride devices on silicon carbide is not limited by the thermal dissipation of the substrate (as may be the case with some devices formed on sapphire). SiC substrates are available from Cree Research, Inc., of Durham, N.C. and methods for producing them are set forth in the scientific literature as well as in U.S. Pat. Nos. Re. 34,861; 4,946,547; and 5,200,022.

Different embodiments of the LED 52 can emit different wavelengths of light depending on the composition of the active region 54 and n- and p-type layer 56, 58. In the embodiment shown, the LED 50 emits a blue light in the wavelength range of approximately 450 to 460 nm. The LED chip 50 can also be covered with one or more conversion materials, such as phosphors, such that at least some of the light from the LED passes through the one or more phosphors and is converted to one or more different wavelengths of light. In one embodiment, the LED chip emits a white light combination of light from the LED's active region and light from the one or more phosphors.

In the case of Group-III nitride devices, current typically does not spread effectively through the p-type layer 58 and it is known that a thin current spreading layer 64 can cover some or the entire p-type layer 58. The current spreading layer helps spread current from the p-type contact across the surface of the p-type layer 58 to provide improved current spreading across the p-type layer with a corresponding improvement in current injection from the p-type layer into the active region. The current spreading layer 64 is typically a metal such as platinum (Pt) or a transparent conductive oxide such as indium tin oxide (ITO), although other materials can also be used. The current spreading layer can have many different thicknesses, with one embodiment of an ITO spreading layer a thickness of approximately 115 nm. The current spreading layer 64 as well as the layers that comprise the composite

layer described below can be deposited using known methods. It is understood that in embodiments where current spreading is not a concern, the composite layer can be provided without a current spreading layer.

Referring now to FIG. 5b, a composite high reflectivity layer 62 can be deposited on the p-type layer 58, and in the embodiment shown the current spreading layer is between the reflectivity layer 62 and the p-type layer. The composite layer 62 according to the present invention has higher reflectivity to the wavelength of light generated by the LED 52 compared to standard metal contacts or distributed Bragg reflectors (DBRs). The composite layer generally comprises a thick layer of material followed by a plurality of thinner layers that combine to provide improved reflectivity. The present invention provides a composite layer with the desired reflectivity that also minimizes the number of layers to minimize the manufacturing complexities and cost.

Referring now to FIG. 6, the different layers that can comprise one embodiment of a composite layer according to the present invention are shown, but it is understood that many different materials, thicknesses and number of layers can also be used. A first layer 66 of the composite layer is provided on the current spreading layer 64, and the first layer can comprise many different materials, with the preferred material comprising a dielectric. Different dielectric materials can be used such as a SiN, SiO<sub>2</sub>, Si, Ge, MgOx, MgNx, ZnO, SiNx, SiOx, alloys or combinations thereof, with the material in first layer 66 in the embodiment shown comprising SiO<sub>2</sub>. This first layer 66 should be relatively thick to provide a reliable viewing angle cut-off point after which the reflectivity of the composite layer is approximately 100%, and in one embodiment used with a blue emitting LED the first layer 66 can have a thickness in the range of 500 to 650 nm, with one embodiment having a thickness of approximately 591 nm.

Referring now to the graph 72 in FIG. 7, which shows the p-polarization reflectivity 74, s-polarization reflectivity 76, and average reflectivity 78 at different viewing angles for a first layer 66 having a thickness in the range of 500 to 650 nm for blue wavelengths of light. The viewing angle cut-off is at a viewing angle of approximately 36 degrees. That is, the reflectivity of the composite layer 62 is approximately 100% at viewing angles greater than approximately 36 degrees, and below this viewing angle the reflectivity can be as low as 94% at certain viewing angles.

Referring again to FIG. 6, to improve reflectivity at lower viewing angles and to improve the angle averaged reflectivity (AAR), the composite layer 62 can also comprise second layers 68a, 68b and third layers 70a, 70b with the second and third layers being made of materials with differing indexes of refraction. In different embodiments different materials can be used for the layers and a different number of layers can be included, with the embodiment shown having two second layers 68a-b comprising SiO<sub>2</sub> and two third layers 70a-b comprising TiO<sub>2</sub>. SiO<sub>2</sub> has an index of refraction of 1.46, while TiO<sub>2</sub> has an index of refraction of 2.34. The two SiO<sub>2</sub> layers can have different thicknesses and the two TiO<sub>2</sub> layers can have different thicknesses, which provide a composite layer that is different from standard DBRs where the layers of different materials have the same thickness. One such example of this type of DBR is a 1/4 wavelength DBR where each of the second and third SiO<sub>2</sub> and TiO<sub>2</sub> layers can have essentially the same optical thickness approximately equal to a 1/4 wavelength of the light. In other embodiments of the composite layer, Ta<sub>2</sub>O<sub>5</sub> can be used in place of TiO<sub>2</sub>.

For the composite layer embodiment shown that is used in conjunction with a blue emitting LED, the second layers 68a-b can have thicknesses in the range of 100 to 120 nm, and

approximately 40 to 60 nm respectively, with one embodiment of the second layers being approximately 108 nm and 53 nm thick. The third TiO<sub>2</sub> layers 70a-b can have thicknesses in the range of 55 to 75 nm and 35 to 55 nm, respectively, with one embodiment having thicknesses of approximately 65 nm and 46 nm respectively.

The composite layer 62 can also comprise a reflective layer 71 on the second layer 68b, deposited using known methods such as sputtering. The reflective layer 71 can have many different thicknesses and can comprise many different reflective materials, with suitable materials being Ag, Al and Au. The choice of material can depend on many factors with one being the wavelength of light being reflected. In the embodiment shown reflecting blue wavelengths of light, the reflective layer can comprise Ag having a thickness of approximately 200 nm. In other embodiments the reflective layer 71 can comprise composite metal layers such as TiAg, NiAg, CuAg or PtAg, and in some embodiments these composite layers can provide improved adhesion to the layer it is formed on, such as the second layer 68b. Alternatively, a thin layer of material such as indium tin oxide (ITO), Ni, Ti or Pt can be included between the second layer 68b and the reflective layer to also improve adhesion.

The structure of the composite layer 62 provides improved AAR compared to standard 1/4 wavelength DBRs. Although there may be a number of reasons why this arrangement provides this improvement, it is believed that one reason is that the different thicknesses of the second layers 68a, 68b and the third layers 70a, 70b present differently to light at various incident angles. That is, light will reach composite layer 62 at many different angles, and at these different angles the second layers 68a, 68b and third layers 70a, 70b can appear as different thicknesses, such as multiples of a 1/4 wavelength thickness depending on the angle. It is believed that the different thicknesses provide the best overall AAR across viewing angles of 0-90 degrees.

FIG. 8 is a graph 80 showing the reflectivity of a composite layer similar to that shown in FIG. 6, and shows the p-polarization reflectivity 82, s-polarization reflectivity 84, and average reflectivity 86 at different viewing angles. In this case, the reflectivity includes the effect of an ITO current spreading layer 64 having a thickness of 115 nm and finite absorption coefficient of 500/cm, which results in the reflectivity approaching but being slightly below 100% at viewing angles greater than approximately 36 degrees. The AAR across viewing angles of 0-90 degrees for the composite layer shown is approximately 98.79%, which provides an improvement over a standard DBR with a similar number of layers made of the same materials. At certain wavelengths of light the AAR of a standard 1/4 wavelength DBR can be approximately 98.73% or less. This difference can have a significant impact on overall LED brightness because light can reflect off the composite layer multiple times before escaping from the LED. This compounding effect of multiple reflections amplifies even small differences in reflectivity.

FIG. 9 shows another embodiment of the composite layer 100 that is similar to composite layer 62 described above and can be used with a blue emitting LED. The composite layer 100 can have four layers instead of five. In this embodiment the first layer 102 is on a current spreading layer 64, although it is understood that the composite layer 100 can be used without a current spreading layer. The first layer 102 is similar to the first layer 66 described above and can be made of many materials and many different thicknesses. In the embodiment shown the first layer 102 can comprise S102 with thickness in the range of 500 to 650 nm, with one embodiment having a thickness of approximately 591 nm.

In this embodiment, the composite layer **100** comprises only one second layer **106** sandwiched between two third layers **108a-b**. Like the embodiment above. That is, there are not an equal number of alternating second layers and third layers as in composite layer **62** described above, and as in conventional DBRs. This results in second and third layers combinations that comprise incomplete pairs or that are asymmetric. In embodiments with incomplete second and third layer pairs can comprise different numbers of each layer such as two second layers and three third layers, three second layers and four third layers, etc.

The second and third layers **106**, **108a-b** can comprise many different materials and can have many different thicknesses. In the embodiment shown, the second layer **106** can comprise SiO<sub>2</sub> and can have a thickness in the range of approximately 100 to 120 nm, with one embodiment having a thickness of 107 nm. The third layers **108a-b** can comprise TiO<sub>2</sub> and can have thicknesses of in the range of 45 to 65 nm and 65 to 85 nm respectively, with one embodiment having third layer thicknesses of approximately 56 and 75 nm, respectively. The composite layer **100** can also comprise a reflective layer **110** on the third layer **108b** that can be deposited using known methods and can comprise the same materials as reflective layer **71** described above.

By having an asymmetric arrangement, the composite layer can have fewer layers with the corresponding reduction in manufacturing steps and costs. This can also provide the additional advantage of better adhesion to subsequent layers, such as a reflective layer **110**. In this embodiment the top layer comprises third layer **108b**, which is TiO<sub>2</sub>. This material can provide improved adhesion to reflective metals compared to the second layer **106** comprising SiO<sub>2</sub>. The composite layer **100**, however, can have a reduced AAR compared to a six-layer arrangement shown in FIG. **6**, with the AAR of one embodiment of a five-layer arrangement as shown in FIG. **9** being approximately 98.61%. This, however, represents an improvement over a standard five layer DBR where the AAR can be approximately 96.61%. Similar to the six-layer embodiment above, this difference can have a significant impact on overall LED brightness because of the compounding effect of multiple reflections.

It is understood that composite layers according to the present invention can have many different layers of different materials and thicknesses. In some embodiments the composite layer can comprise layers made of conductive materials such as conductive oxides. The conductive oxide layers can have different indices of refraction and the differing thicknesses to provide the improved reflectivity. The different embodiments can have different arrangements of complete and incomplete pairs of second and third layers. It is also understood that the composite layer can be arranged in different locations on an LED and can comprise different features to provide thermal or electrical conduction through the composite layer.

Referring now the FIGS. **10a** through **10d**, another embodiment of an LED **120** having many of the same features as LED **50** shown in FIGS. **5a** and **5b** and for those same features the same reference numbers will be used. The LED **50** is fabricated such that it can be arranged in a flip-chip orientation, so for this embodiment the end LED chip will have the composite layer **62** (or composite layer **100**) arranged as an internal layer as further described below. Accordingly, an electric signal should pass through the composite layer **62**. Referring now to FIG. **10a** and FIG. **11**, holes **122** can be formed through the composite layer **62** at random or regular intervals, with the holes sized and positioned so that

a conductive material can be deposited in the holes to form conductive vias. In the embodiment shown the holes **122** are at regular intervals.

In different embodiments having a current spreading layer **64**, the holes **122** may or may not pass through the current spreading layer **64**. The holes **122** can be formed using many known processes such as conventional etching processes or mechanical processes such as microdrilling. The holes **122** can have many different shapes and sizes, with the holes **122** in the embodiment shown having a circular cross-section with a diameter of approximately 20 microns. Adjacent holes **122** can be approximately 100 microns apart. It is understood that the holes **122** (and resulting vias) can have cross-section with different shapes such as square, rectangular, oval, hexagon, pentagon, etc. In other embodiments the holes are not uniform size and shapes and there can be different spaces between adjacent holes.

Referring now to FIG. **12**, instead of holes an interconnected grid **124** can be formed through the composite layer **62**, with a conductive material then being deposited in the grid **124** to form the conductive path through the composite layer. The grid **124** can take many different forms beyond that shown in FIG. **11**, with portions of the grid interconnecting at different angles in different embodiment. An electrical signal applied to the grid **124** can spread throughout along the interconnected portions. It is further understood that in different embodiments a grid can be used in combination with holes.

Referring now to FIG. **10b**, a conductive layer **126** can be deposited on the composite layer **62** covering its reflective layer and filling the holes **122** to form vias **128** through the composite layer **62**. In other embodiments, the conductive layer can cover less than all of the composite layer **62**. The conductive layer **126** can comprise many different materials such as metals or conductive oxides, both of which can be deposited using known techniques.

Referring now to FIG. **10c**, the LED **120** can be flip-chip mounted to a submount **130** using known mounting techniques. In the embodiment shown, the LED **50** is flip-chip mounted to the submount by a conductive bond material **132**. It is understood that in embodiments where the LEDs chips **120** are formed at the wafer level and then singulated, the LEDs chips **120** can be wafer bonded to the submount **130** using known wafer bonding techniques. The submount **130** can be made of many different materials and can have many different thicknesses, with the preferred submount **130** being electrically conductive so that an electrical signal can be applied to the active region of the LED through the submount **130**. The signal also passes through the composite layer along conductive vias **128**.

Referring now to FIG. **10d**, the growth substrate **60** (as shows in FIG. **10c**) can be removed using known grinding and/or etching processes. A first contact **134** can be deposited on the n-type layer **56** and a second contact **136** can be deposited on the submount **130**. The first and second contacts **134**, **136** can comprise many different materials such as Au, copper (Cu) nickel (Ni), indium (In), aluminum (Al), silver (Ag), or combinations thereof. In still other embodiments the first and second contacts can comprise conducting oxides and transparent conducting oxides such as ITO, nickel oxide, zinc oxide, cadmium tin oxide, indium oxide, tin oxide, magnesium oxide, ZnGa<sub>2</sub>O<sub>4</sub>, ZnO<sub>2</sub>/Sb, Ga<sub>2</sub>O<sub>3</sub>/Sn, AgInO<sub>2</sub>/Sn, In<sub>2</sub>O<sub>3</sub>/Zn, CuAlO<sub>2</sub>, LaCuOS, CuGaO<sub>2</sub> and SrCu<sub>2</sub>O<sub>2</sub>. The choice of material used can depend on the location of the contacts as well as the desired electrical characteristics such as transparency, junction resistivity and sheet resistance. The top surface of the n-type layer **56** can be textured or shaped

such as by laser texturing, mechanical shaping, etching (chemical or plasma), scratching or other processes, to enhance light extraction.

During operation, an electrical signal is applied to the LED **50** across first and second contacts **134**, **136**. The signal on the first contact **134** spreads into the n-type layer **56** and to the active region **54**. The signal on the second contact **136** spreads into the submount **130**, through composite layer **62** along the vias **128**, through the current spreading layer **64**, into the p-type layer **58** and to the active region **54**. This causes the active region **54** to emit light and the composite layer **62** is arranged to reflect light emitted from the active region toward the submount **128**, or reflected by TIR toward the submount **130**, back toward the top of the LED chip **50**. The composite layer **62** encourages emission toward the top of the LED chip **50** and because of its improved reflectivity, reduces losses that occur during reflection.

It is understood that the composite layers can be used in many different ways and in many different locations on LEDs, LED chips, and other solid-state emitters. As shown in FIGS. **13a** and **13b**, the composite layers can be used in conjunction with a lateral geometry LED chip **150** where both contacts are on one side of the LEDs. The layers of the LED **150** are generally the same as those for LED chip **50** and can comprise an active layer/region **154** sandwiched between n-type and p-type oppositely doped epitaxial layers **156**, **158**, all of which are formed successively on a growth substrate **160**. For lateral geometry LEDs, a portion of the p-type layer **158** and active region **154** is removed, such as by etching, to expose a contact mesa **161** on the n-type layer **156**. In this embodiment, a composite layer **162** similar to the composite layer **62** described above can be included on both the surface of the n-type layer **156** and the surface of the p-type layer **158**, with the composite layer having a metal layer **164** and conductive vias **166** similar to the metal layer **126** and vias **128** described above.

Referring now to FIG. **13b**, the LED chip **150** can be flip-chip mounted to a submount **168** using known mounting processes preferably by conductive bonds **170** to the metal layers **164** on the composite layers **162**. An electrical signal from the submount **168** is applied to the LED through the conductive bonds **170**, and composite layers **162**, causing the LED chip to emit light. The composite layers **162** reflect light that is directed toward the submount **168** to reflect back toward the emission surface of the LED chip **150**. The improved reflectivity of the composite layers **162** reduces reflectivity losses and improves overall emission efficiency of the LED chip **150**.

FIG. **14** shows still another embodiment of LED **180** according to the present invention also having an active layer/region **184** sandwiched between n-type and p-type oppositely doped epitaxial layers **186**, **188**, all of which are formed successively on a growth substrate **190**. A portion of the p-type layer **188** and active region **184** is removed, such as by etching, to expose a contact mesa on the n-type layer **186**. In this embodiment, p- and n-type contacts **192**, **194** are deposited on the p-type layer **188** and the contact mesa of the n-type **186**, and a composite layer **196** can be included on the bottom surface of the substrate **190**.

In this embodiment, an electrical signal is not applied to the LED through the composite layer **196**. Instead, the electrical signal is applied through the p- and n-type contacts **192**, **194** where it spreads laterally to the active region **184**. As a result, an electrical signal does not need to pass through the composite layer **196** and the composite layer **196** does not need electrically conductive vias. Instead, an uninterrupted composite layer can be included across the substrate bottom sur-

face to reflect light emitted from the active region toward the substrate and TIR light that reflects toward the substrate. It is understood that in different embodiments the composite layer can also cover all or part of the side surfaces of the LED **180**, and a composite layer can be used in with the n- and p-type contacts **192**, **194** to improve their reflectivity.

It is also understood that a composite layer can also be used on the bottom surface of submounts in flip-chip embodiments where the submounts are transparent. In these embodiments the desired reflectivity can be achieved without having internal composite layers **162** as shown in FIG. **13b**.

FIG. **15** shows still another embodiment of an LED chip **210** having an active layer/region **214**; n-type and p-type oppositely doped epitaxial layers **216**, **218**, all of which are formed successively on a growth substrate **220**. LED **210** has vertical geometry with a p-type contact **224** on the p-type layer **218**. A thin semitransparent current spreading layer (not shown) can cover some or the entire p-type layer **218**, which is typically a metal such as Pt or a transparent conductive oxide such as ITO, although other materials can also be used. A composite layer **226** is included on the substrate **220** and, because the LED **210** has vertical geometry, an electrical signal can be applied to the LED through the composite layer **226**. The composite layer comprises conductive vias **228** similar to those described above that allow an electrical signal to pass through the composite layer **226**. The composite layer **226** can also comprise a metal layer **230** with an n-type contact **232** on the metal layer. This embodiment is particularly applicable to LEDs having electrically conductive substrates and an electrical signal applied to the p-type **224** and n-type contact **232** spreads to the LED active region **214** causing it to emit light. It is also understood that a composite layer can be included with the p-type contact to improve its reflectivity.

In different embodiments of the present invention the vias can serve additional purposes beyond conducting electrical signals. In some embodiments the vias can be thermally conductive to assist in thermal dissipation of heat generated by the LED. Heat can pass away from the LED through the vias where it can dissipate.

Although the present invention has been described in detail with reference to certain preferred configurations thereof, other versions are possible. Therefore, the spirit and scope of the invention should not be limited to the versions described above.

We claim:

1. A light emitting diode (LED) chip, comprising:
  - an active region between two oppositely doped layers;
  - a composite high reflectivity layer arranged to reflect light emitted from said active region, said composite layer comprising:
    - a first layer;
    - one or more second layers and a plurality of third layers on said first layer, said second layers having an index of refraction different from said third layers, wherein at least one of said second layers is interposed between two of said third layers, and each of said third layers having different thicknesses compared to the other of said third layers; and
    - a reflective layer on the topmost of said second and third layers;
  - wherein said composite high reflectivity layer is on a side of a substrate opposite said active region.
2. The LED chip of claim 1, wherein said first layer comprises a dielectric material.
3. The LED chip of claim 1, wherein said first layer is thicker than the thickest of said second and third layers.

4. The LED chip of claim 1, wherein said first layer is at least three times thicker than the thickest of said second and third layers.

5. The LED chip of claim 1, wherein said first layer has a thickness in the range of 500 to 650 nanometers. 5

6. The LED chip of claim 1, further comprising a current spreading layer.

7. The LED chip of claim 6, wherein said current spreading layer comprises indium tin oxide (ITO).

8. The LED chip of claim 1, wherein said one or more 10 second layers comprise silicon dioxide (SiO<sub>2</sub>).

9. The LED chip of claim 1, wherein said one or more second layers comprise two second layers.

10. The LED chip of claim 9, wherein the first of said two second layers has a thickness in the range of 100 to 120 15 nanometers and the second of said two second layers has a thickness in the range of 40 to 60 nanometers.

11. The LED chip of claim 1, wherein said plurality of third layers comprise titanium dioxide (TiO<sub>2</sub>).

12. The LED chip of claim 1, wherein said plurality of third 20 layers comprise two third layers.

13. The LED chip of claim 12, wherein the first of said two third layers has a thickness in the range of 55 to 75 nanometers and the second of said two third layers has a thickness in the range of 35 to 55 nanometers. 25

14. The LED chip of claim 1, wherein said composite layer further comprises holes.

15. The LED chip of claim 14, wherein said holes are filled with a conductive material.

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